

classical
gaseous

The Quad: a general purpose modular readout system for TPCs

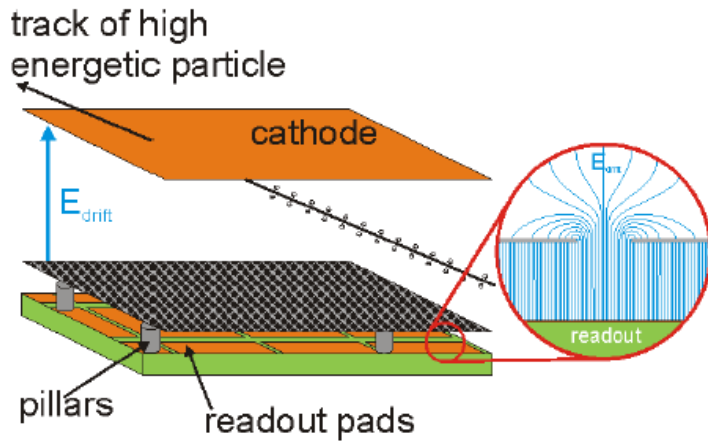
+ reaching transmission secondary electron yield TSEY = 5.2

Harry van der Graaf
Nikhef & TU Delft

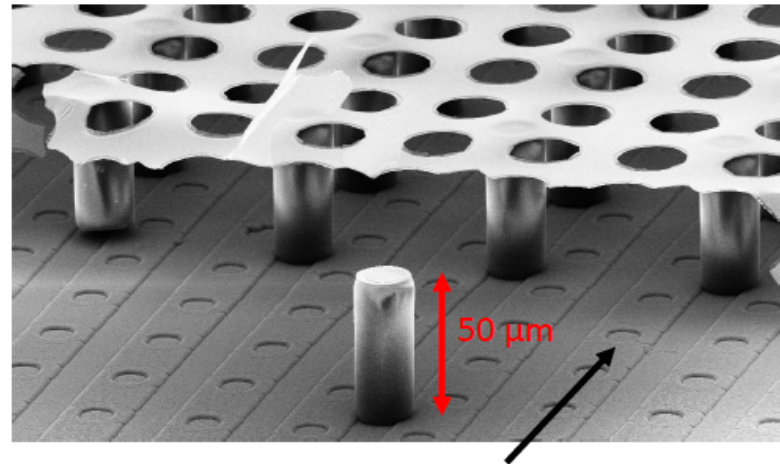
8th Symposium on Large TPCs
Diderot University
Paris, France, Dec 6 2016

From Micromegas to GridPix Detectors

Micromegas



GridPix



Standard charge collection:

- Pads of several mm²
- Long strips (~10 cm length, ~200 μm pitch)

Diffusion within gas amplification region:

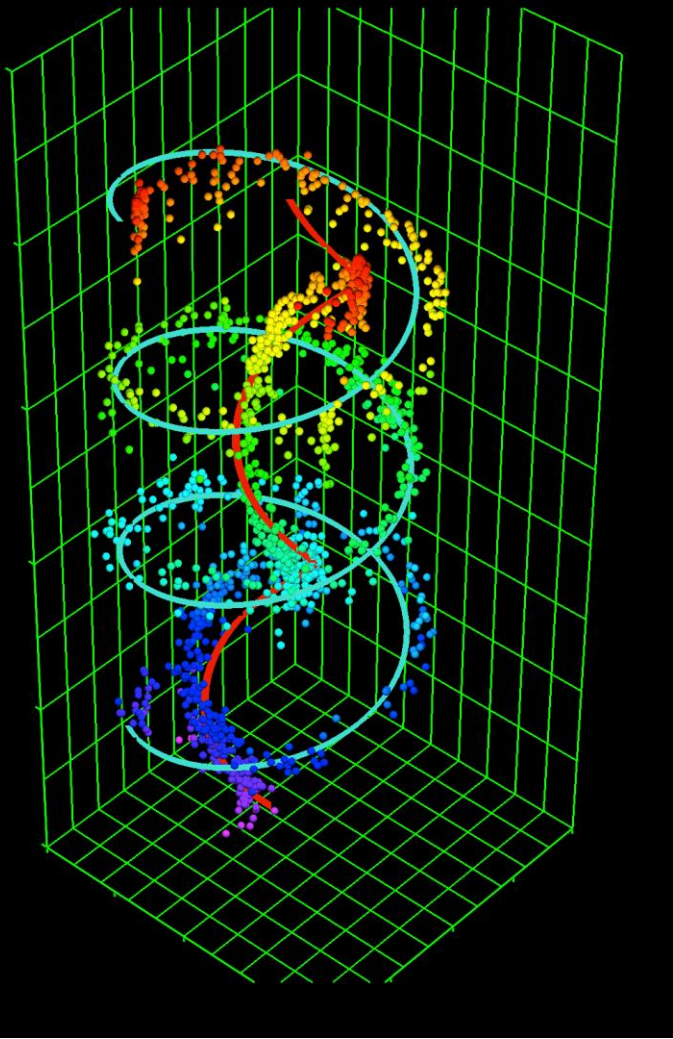
- Ar:CH₄ 90:10 → σ ≈ 25 μm
- Ar:iC₄H₁₀ 95:5 → σ ≈ 25 μm

Smaller pads/pixels should improve spatial resolution
Invention of the GridPix in 2006 at Nikhef



Use bump bond pads of a readout ASIC as charge collecting anodes

Production of Micromegas structure directly on top of pixelized readout ASIC through photolithographic postprocessing



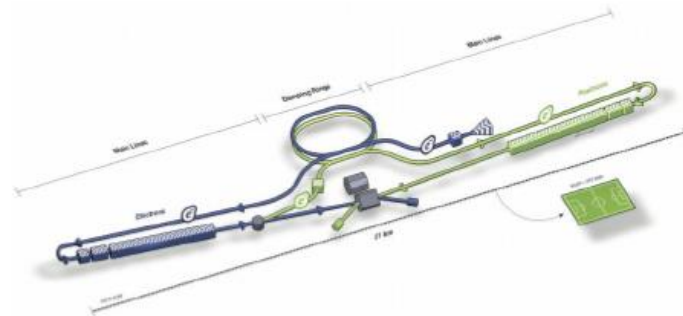
2007: GridPix with functioning protection layer
the ultimate TPC detector:

- single electron sensitive
- extract ALL info of primary electrons in gas
- only gas diffusion limits TPC performance
- (and pixelsize)

2007 – 2016:

1. attempt GridPix mass production on wafers: wafer post processing (InGrid)
2. Improve protection layer: no faults permitted

Applications III – Large Area GridPix Detector

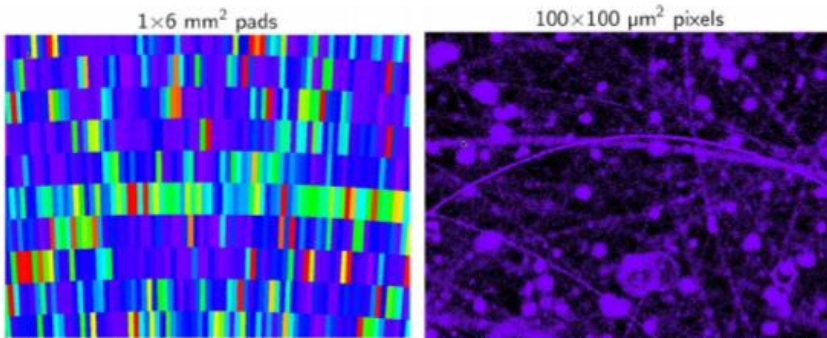
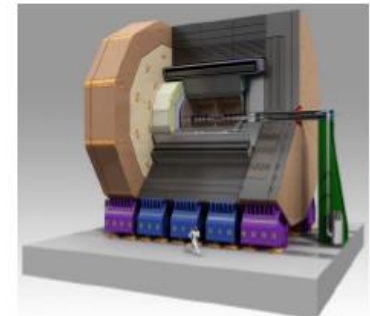


International Linear Collider:

- Linear e^+e^- collider with $\sqrt{s} = 500 \text{ GeV} - 1 \text{ TeV}$

International Large Detector:

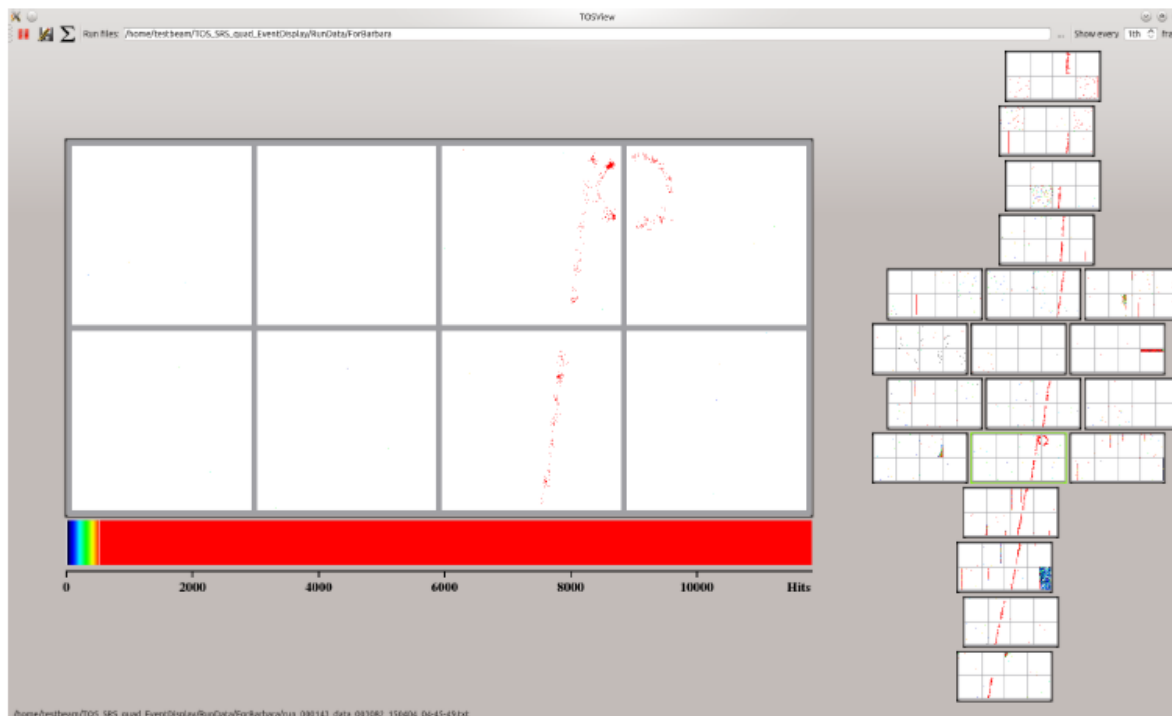
- One of two ILC general purpose detectors
- Foresees a central TPC as main tracker



Simulation for the CLIC detector, M. Killenberg, LCD-Note-2013-005

- High occupancy through background processes ($\gamma\gamma \rightarrow \text{hadrons}$, $e^+e^- \rightarrow \text{pairs/beam halo}$)
- Use of GridPixes would minimize the occupancy
 - better track finding, δ -ray removal
 - improved dE/dx by primary e^- counting
 - pad plane and readout electronics fully integrated
- For full readout of ILD-TPC about 50,000 to 60,000 GridPixes are needed (2 endcaps with 10 m^2 each)
 - need to prove large area coverage and scalability

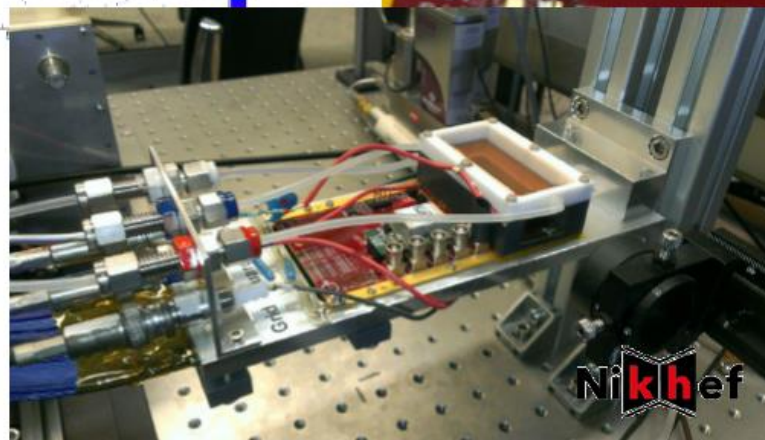
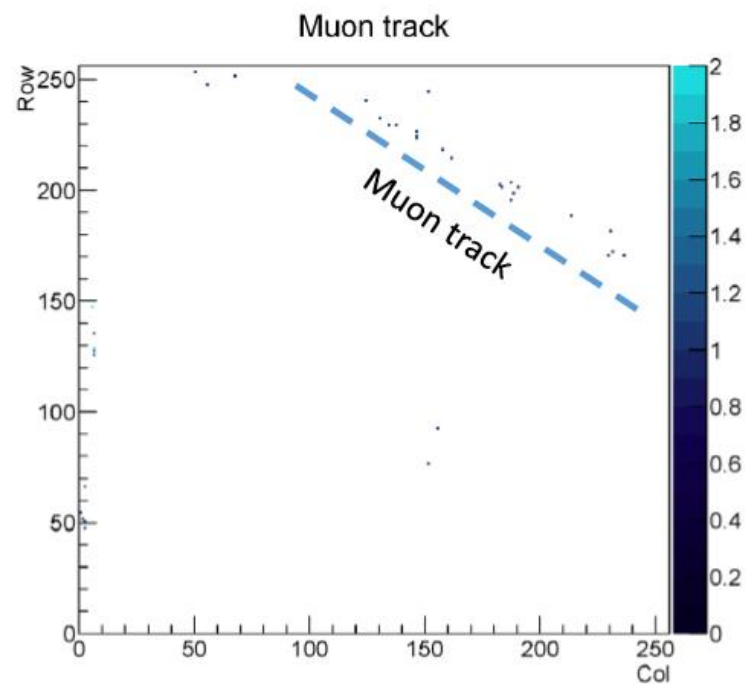
Applications III – Large Area GridPix Detector



First Timepix3 GridPix

In collaboration with Nikhef LEPCOL group:
F. Hartjes, K. Heijhof, P. Kluit, G. Raven,
J. Timmermans, S. Tsigaridas, H. van der Graaf

- First Timepix3 wafer has been successfully processed at IZM Berlin
- First tests with Timepix3 GridPix were performed at Nikhef some days ago



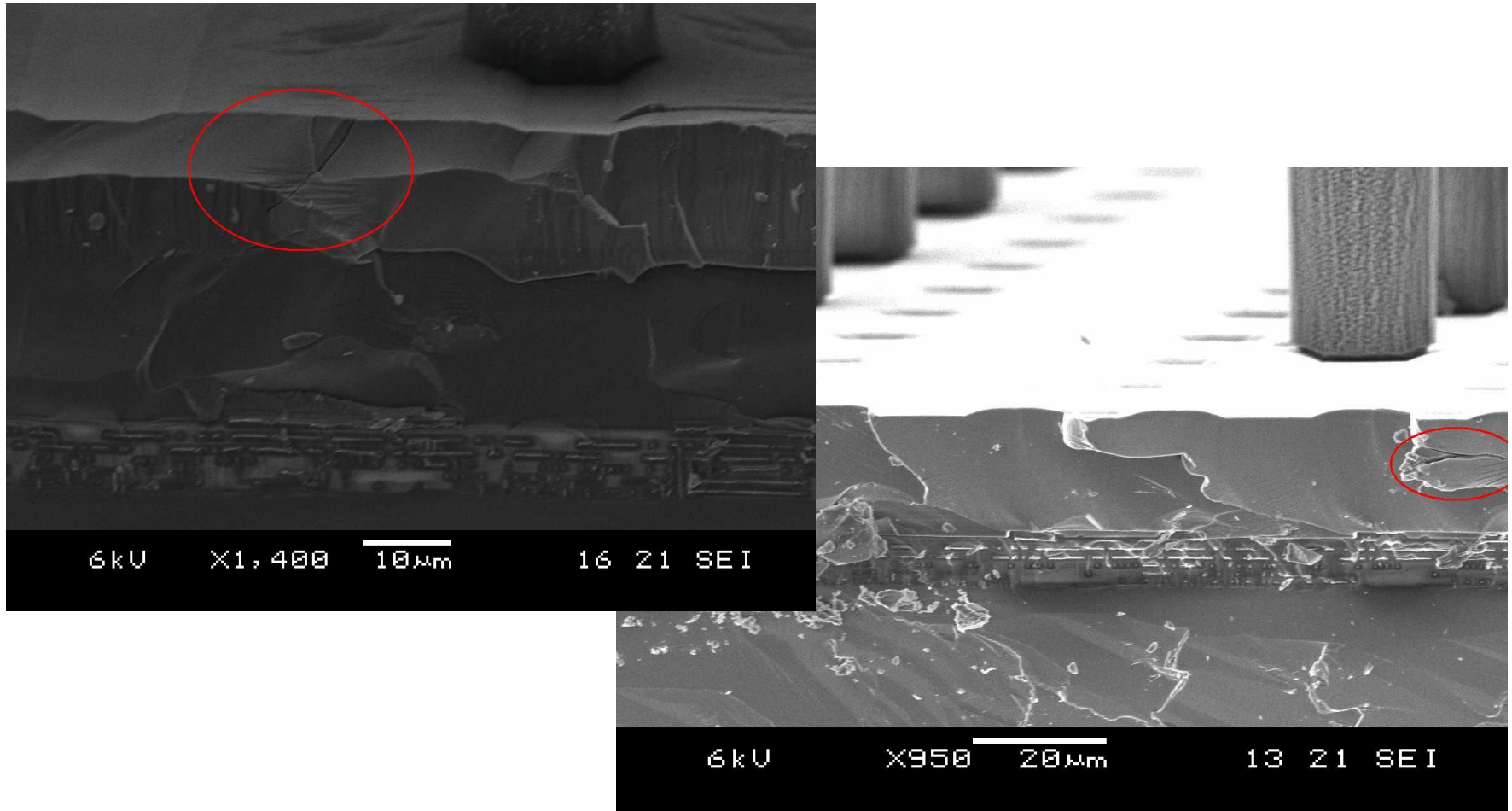


Fig 6. SEM images of a cut-open GridPix chips, clearly showing the SiNitride protection layer on top of the chip, of which its metal layers are well visible. A fault in the form of a cavity is identified and indicated.

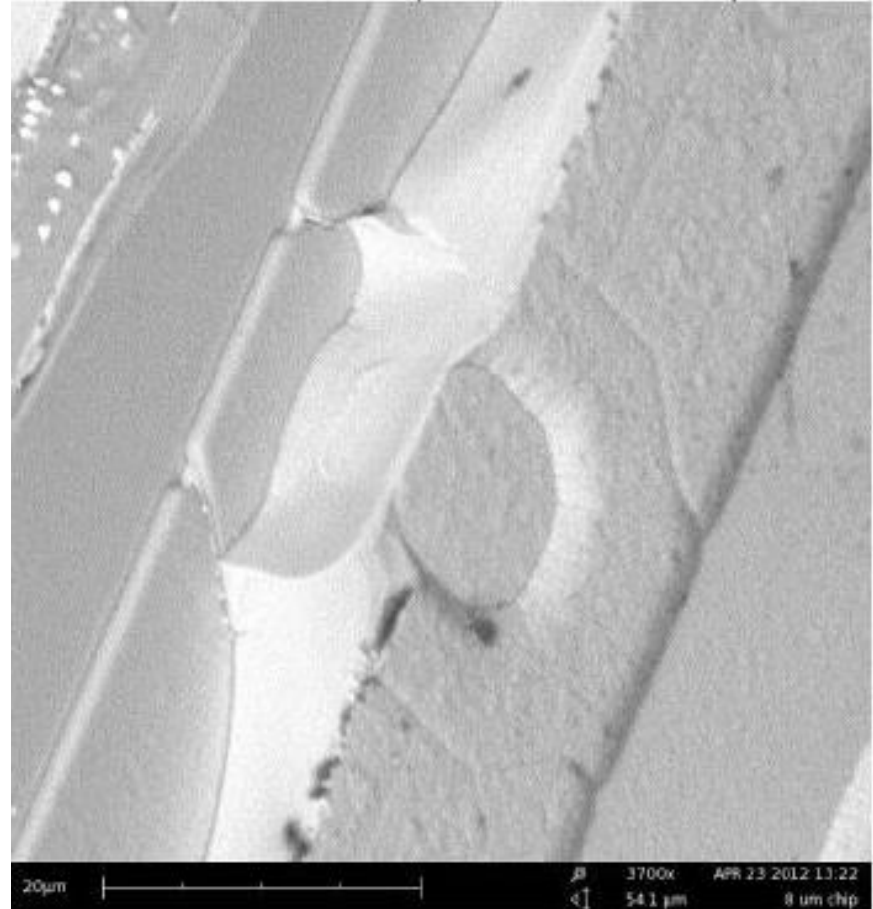
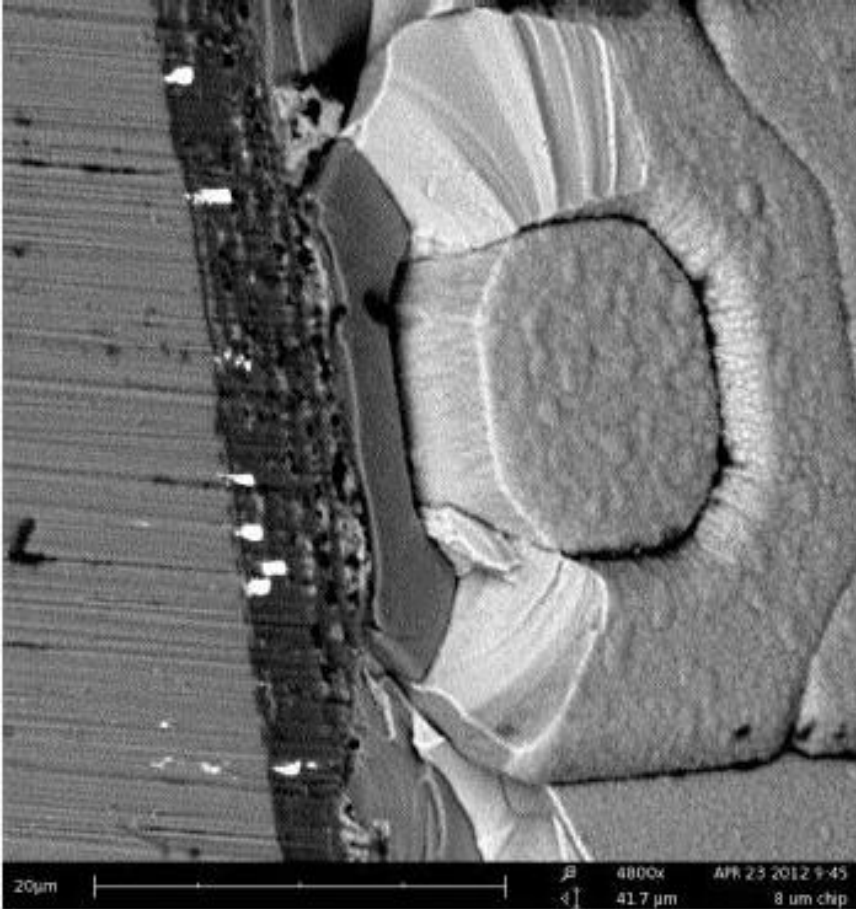
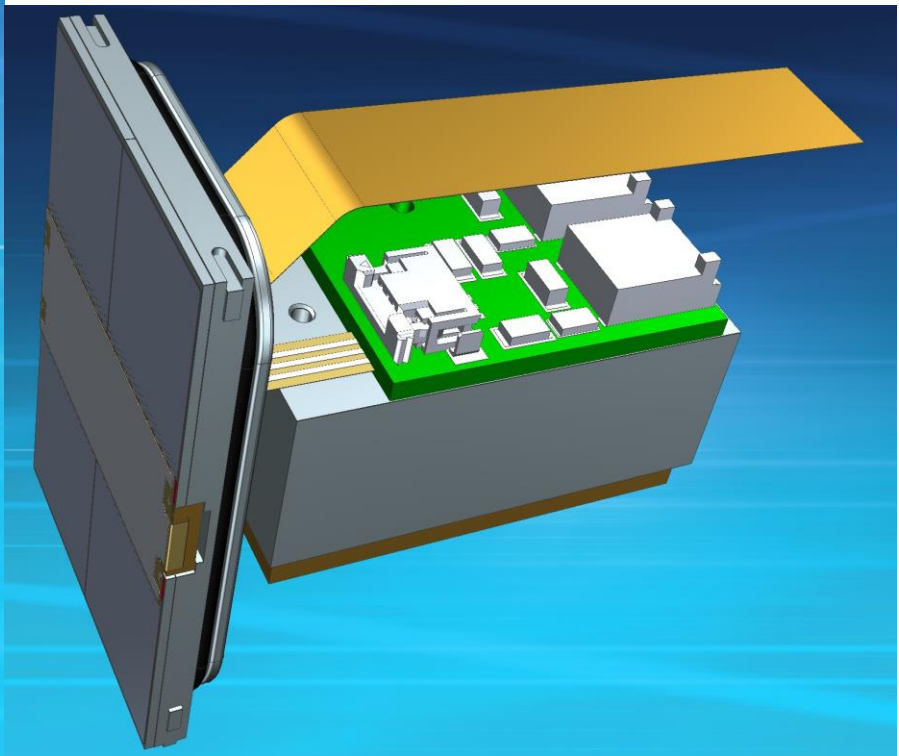
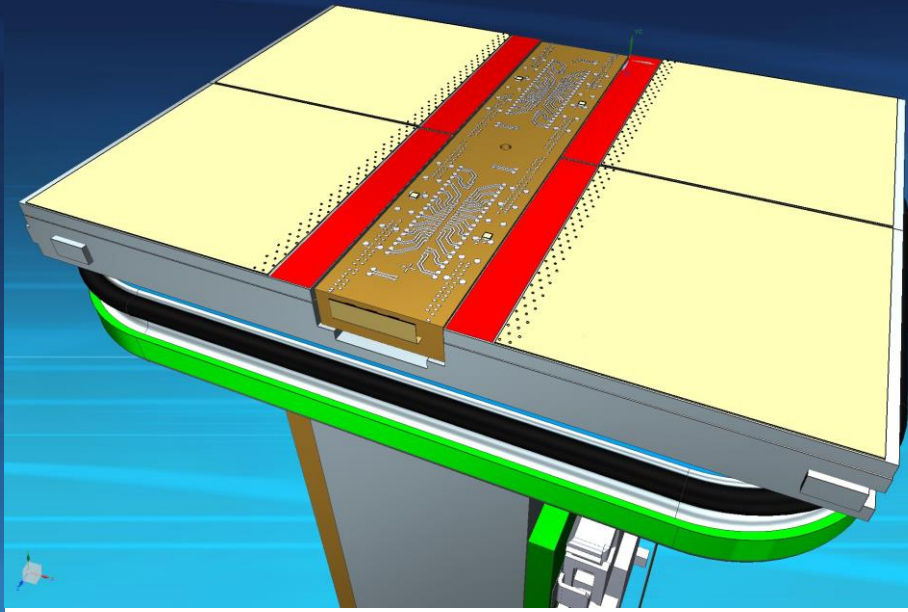
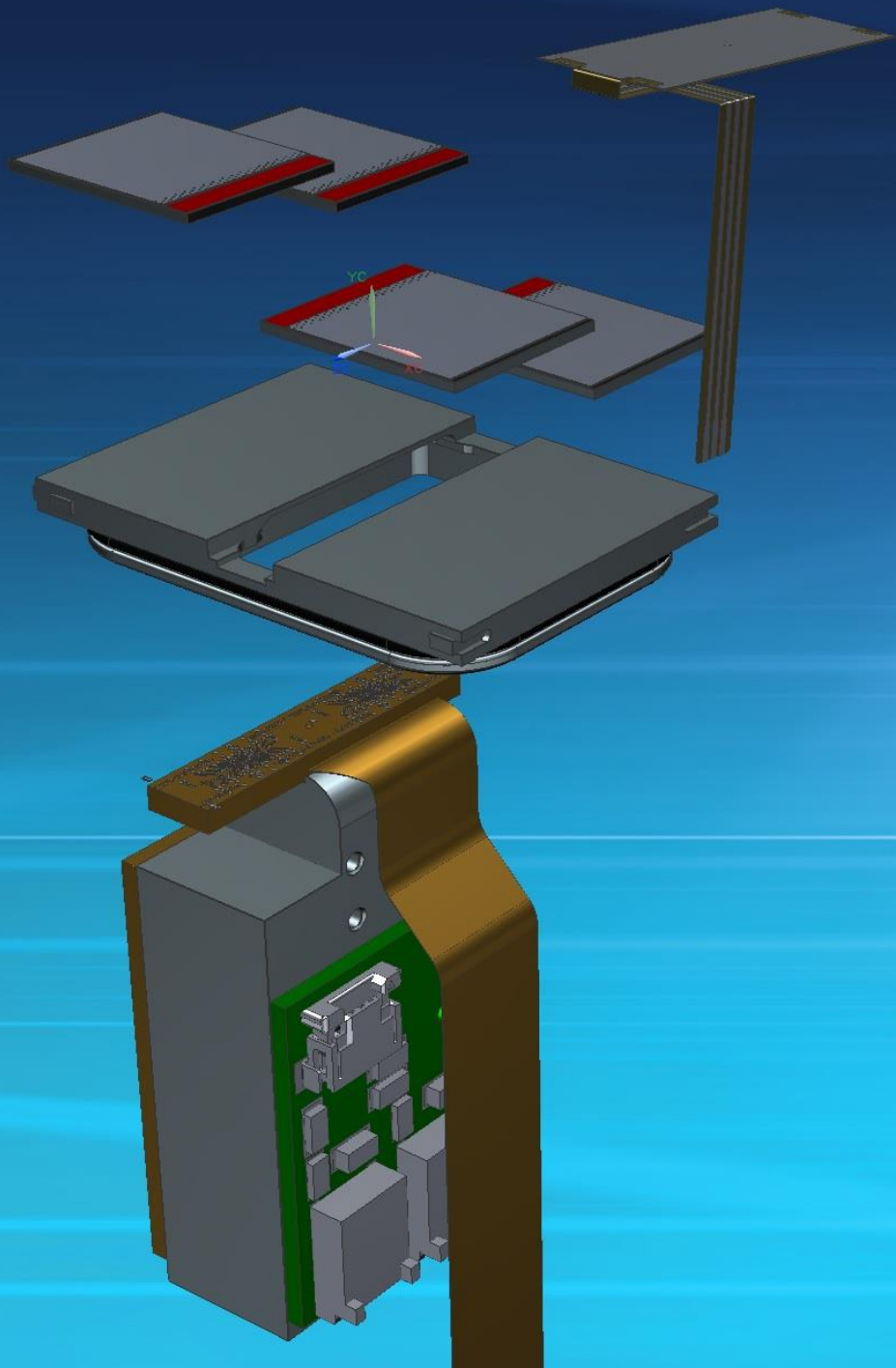
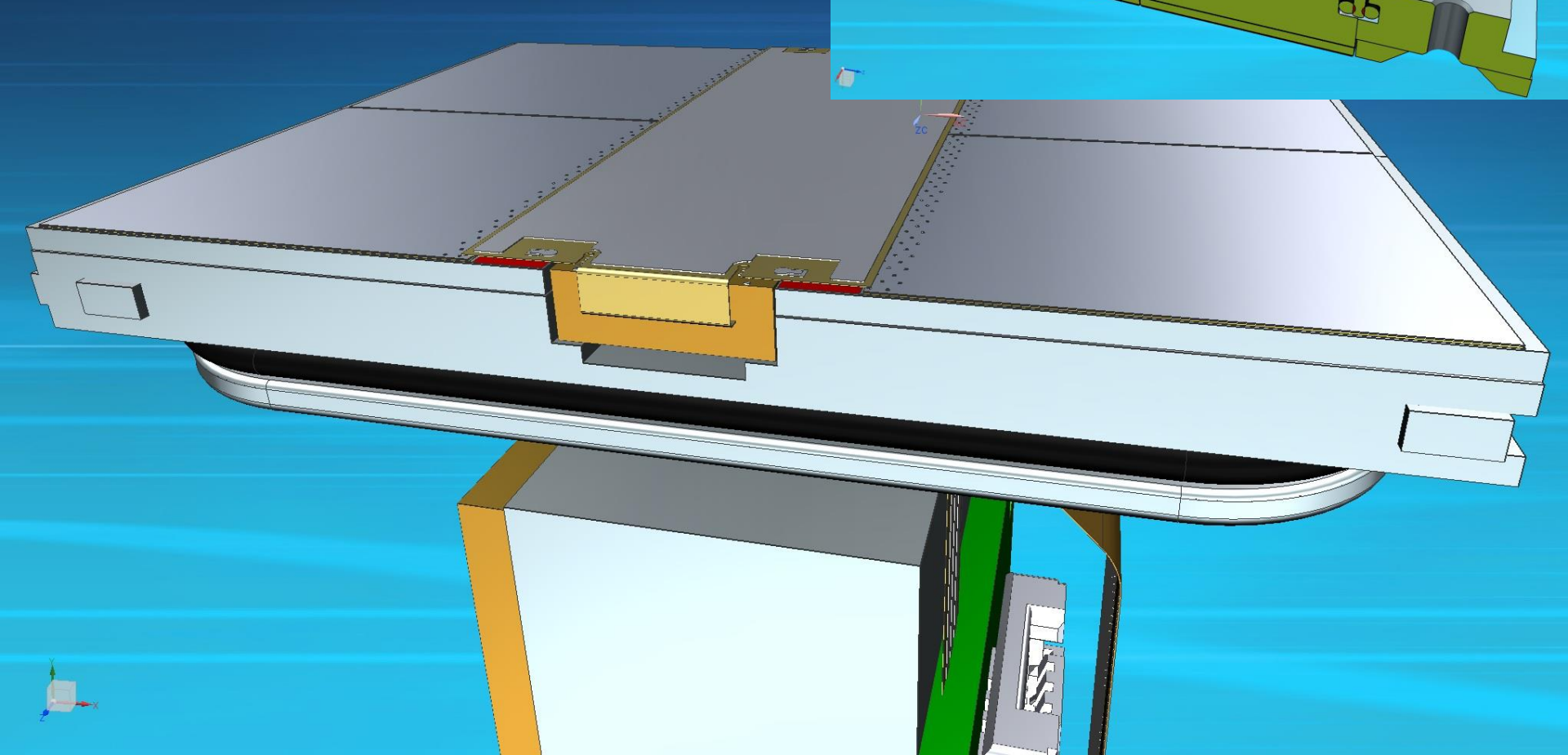
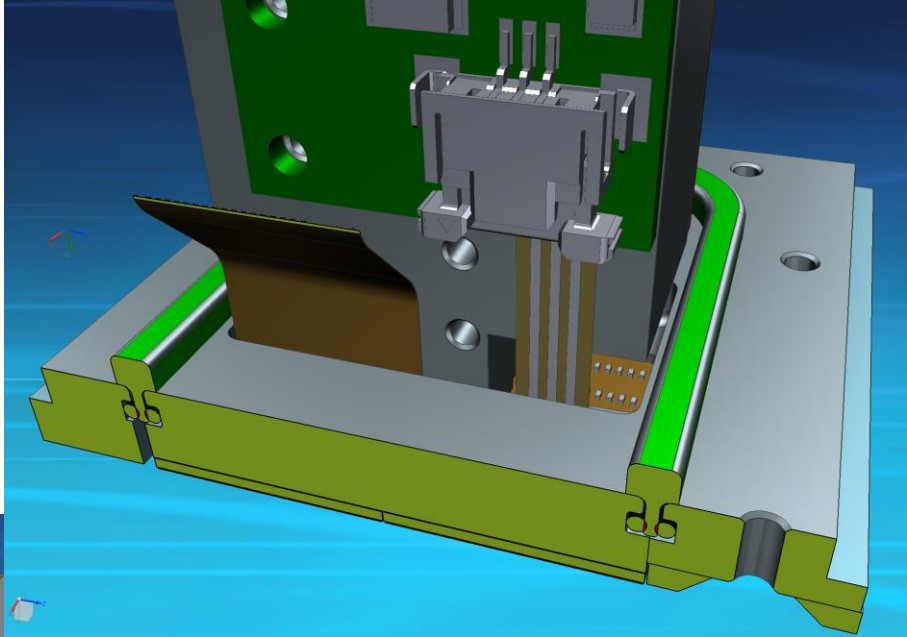
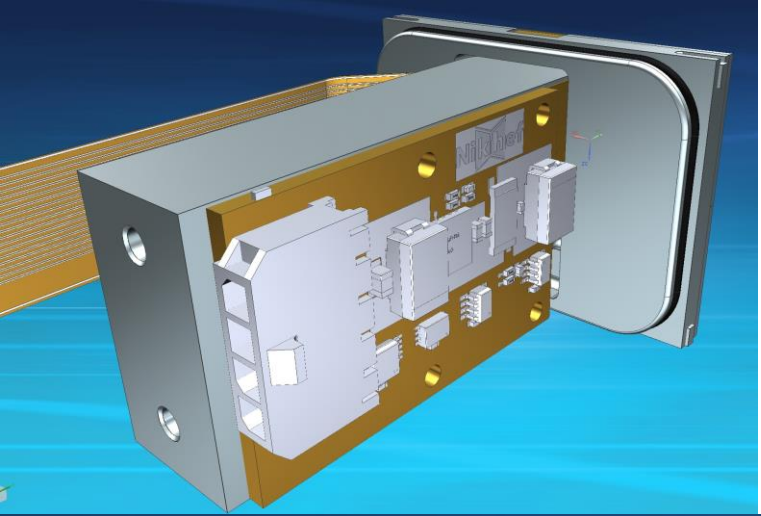


Fig 7. The pixel input pads of the TimePix 1 chip cause a well-known irregularity acting as seed for a cavity (defect) in a protection layer to be deposit. Left: edge variation seeds cavity, right: no problem

New opportunity:

- IZM-Berlin can now (2016) make much better (fault free) SiNitride protection layer
 - A series of Timepix-3 based GridPixes has been made, better discharge proof
 - Bonn and Nikhef have started the LepCol project: GridPix for the TPC for ILC
-
- Modular system: small basic surface modules, exchangeable, repairable
 - Large number of feedthrough's (50/GridPix chip)
 - cooling required
 - Readout with SPIDRE system; each Quad connected with multichannel Concentrator





- single primary electron sensitive
- electron detection efficiency > 90 %
- data driven hit-pixel output @ 2.2 Gb/s
- modular system: basic unit includes 4 TPX-3 GridPix (28 mm x 40 mm)
- fiducial surface: 60 % of total (peripheral electronics & wire bonds (TSV!))

- Should become available for third users
- Future new versions:
 - larger basic units
 - better surface efficiency: Through Silicon Via's (TSVs), reduced peripheral area

Drift Field Focusing

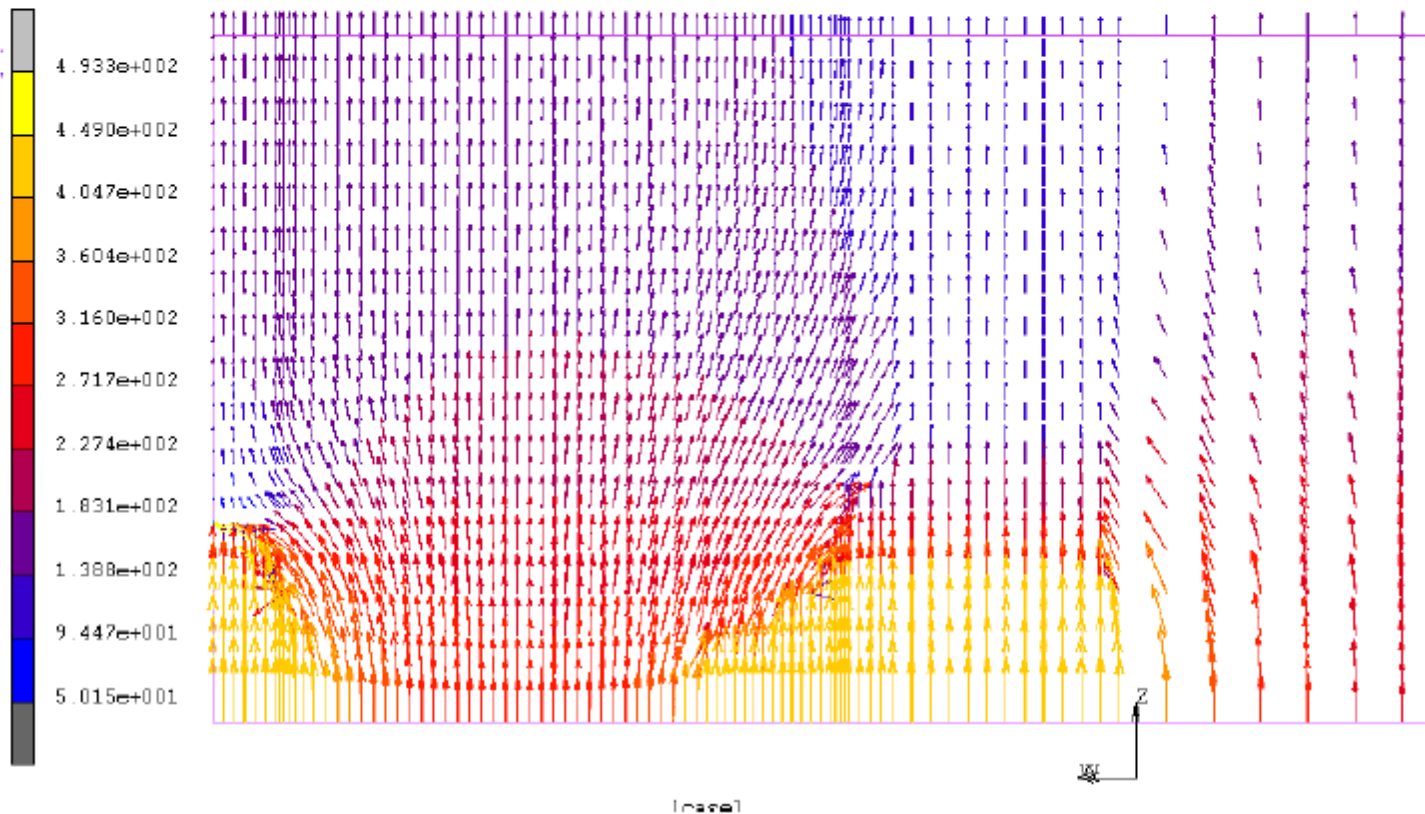
'dead' area between GridPix fiducial areas
distortion of electric drift field

What about a controlled drift field distortion?
Focusing may reduce dead area

QuadFocus

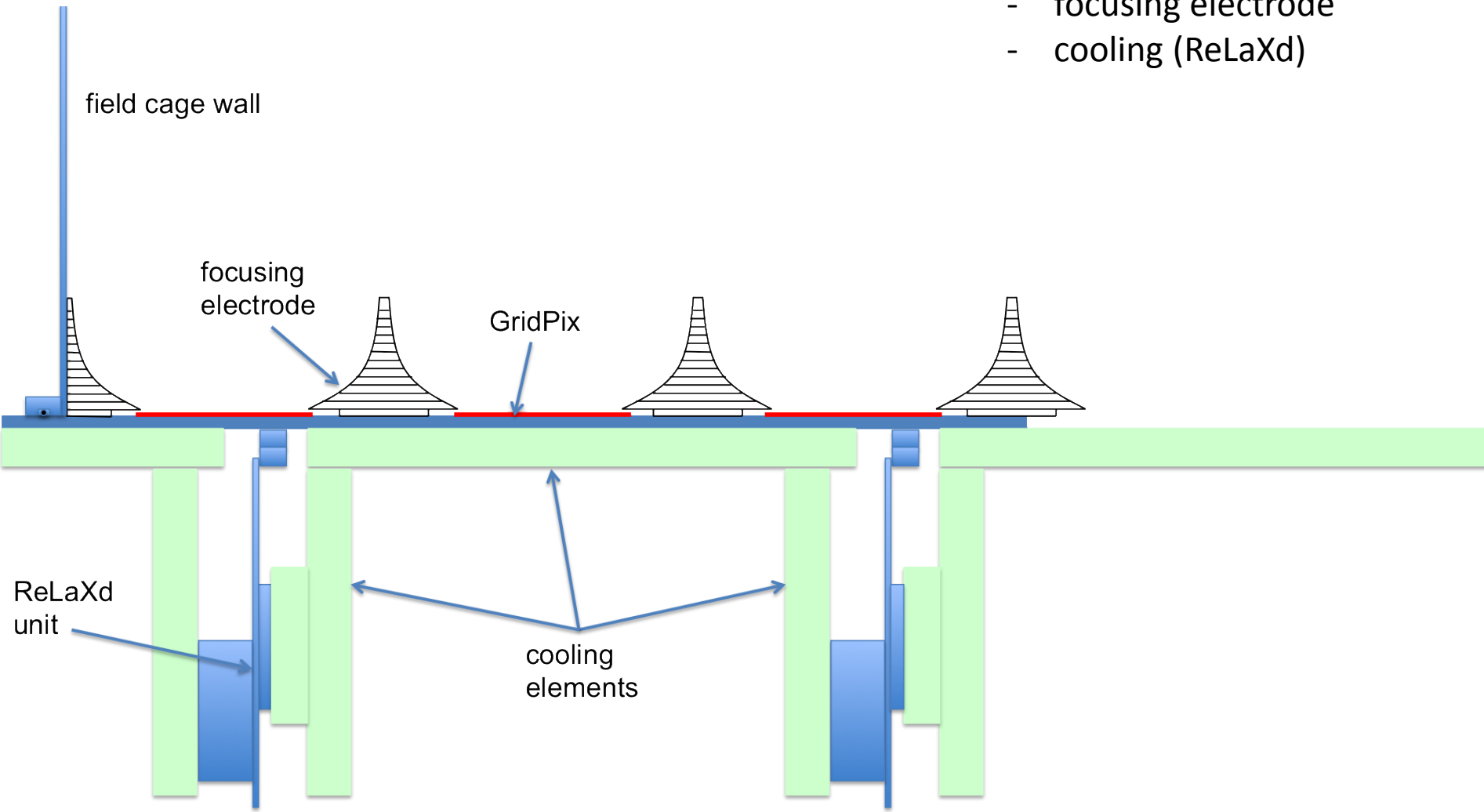
- 3D simulation
- Upper part homogeneous E-field
- Lower part controlled focused E-field

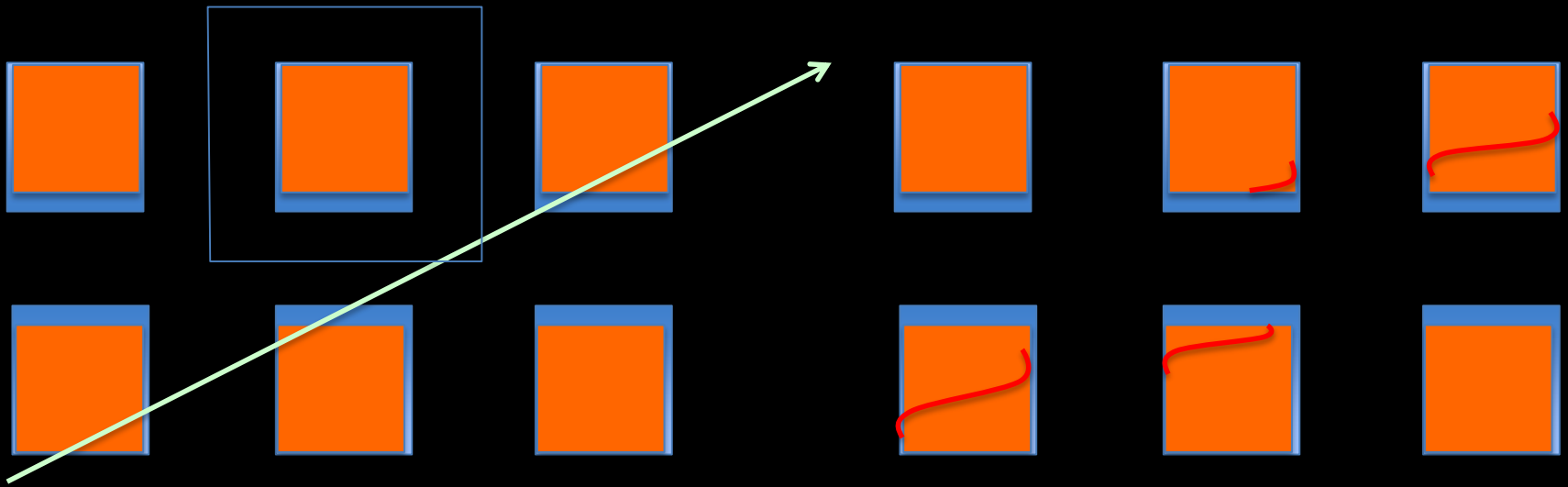
Inc: 1
Time: 1.000e+000



work:

- pcb
- focusing electrode
- cooling (ReLaXd)

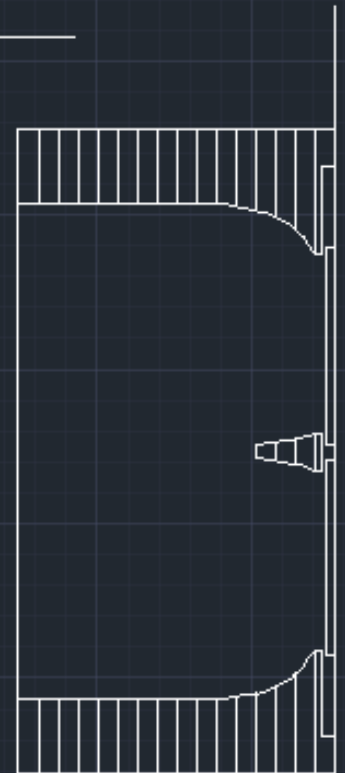
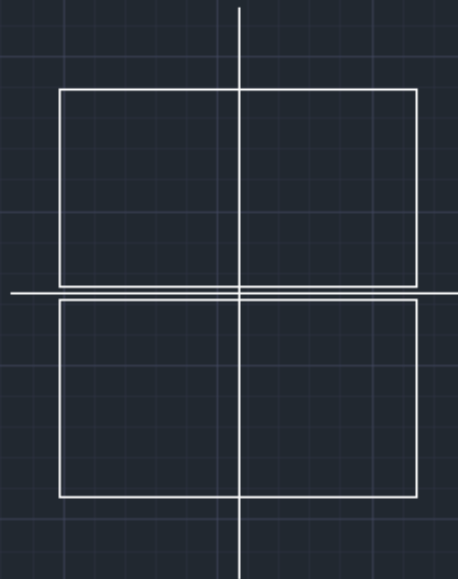
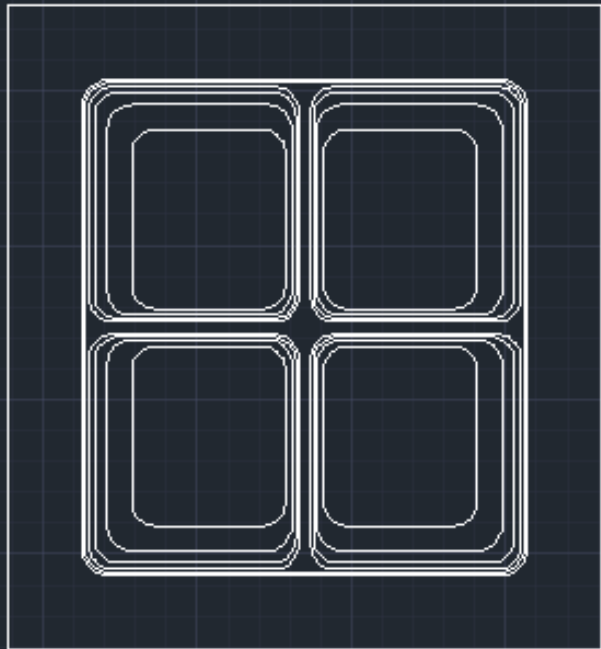
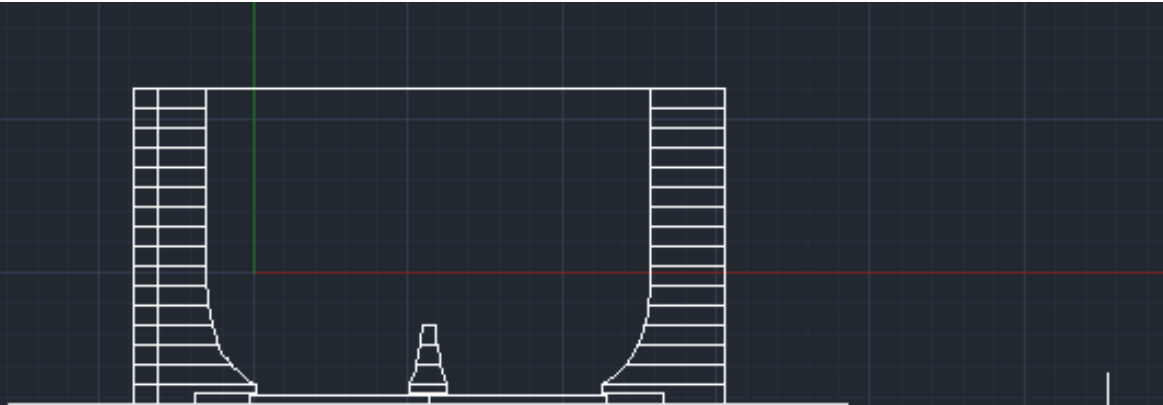
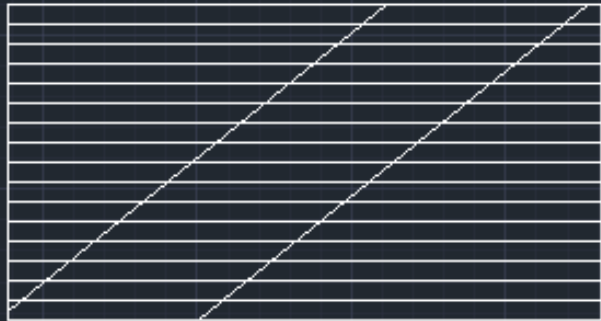




Autocalibration

- get initial $f(X,Y) \rightarrow (X',Y')$ from 3D e-field
- make scatter plots of residuals
- modify $f(X,Y)$ until residuals are minimized

Basic correction: $X' = C X, Y' = C Y$
+ $E \times B$ effect

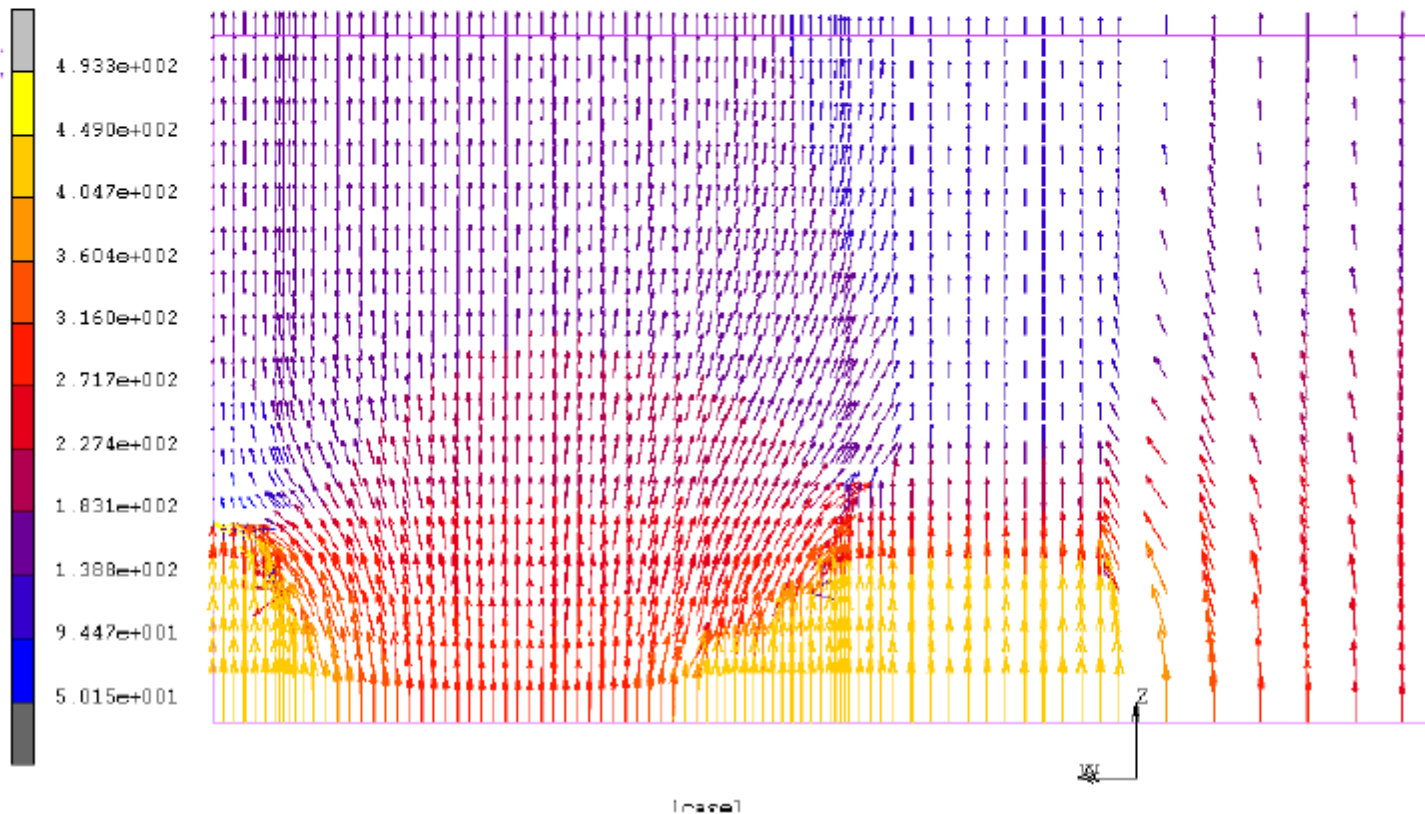


Focusing drifter for Quad TimePix on ReNexd

QuadFocus

- 3D simulation
- Upper part homogeneous E-field
- Lower part controlled focused E-field

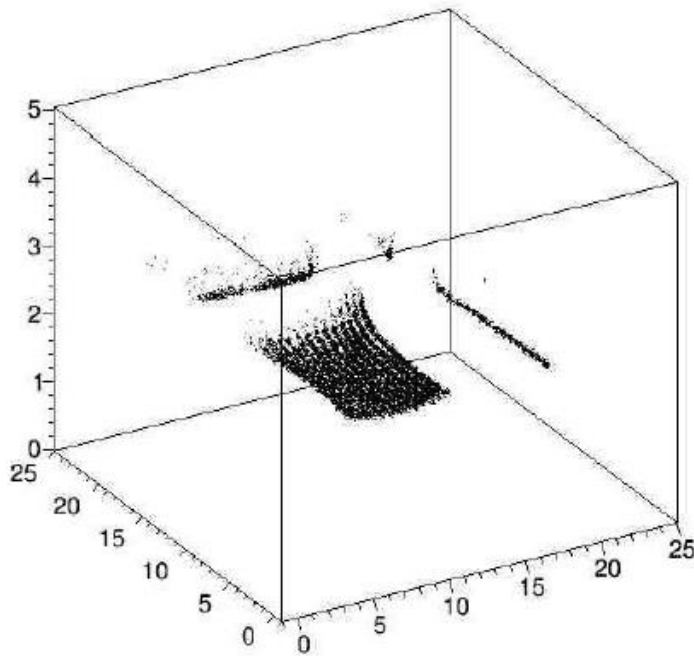
Inc: 1
Time: 1.000e+000



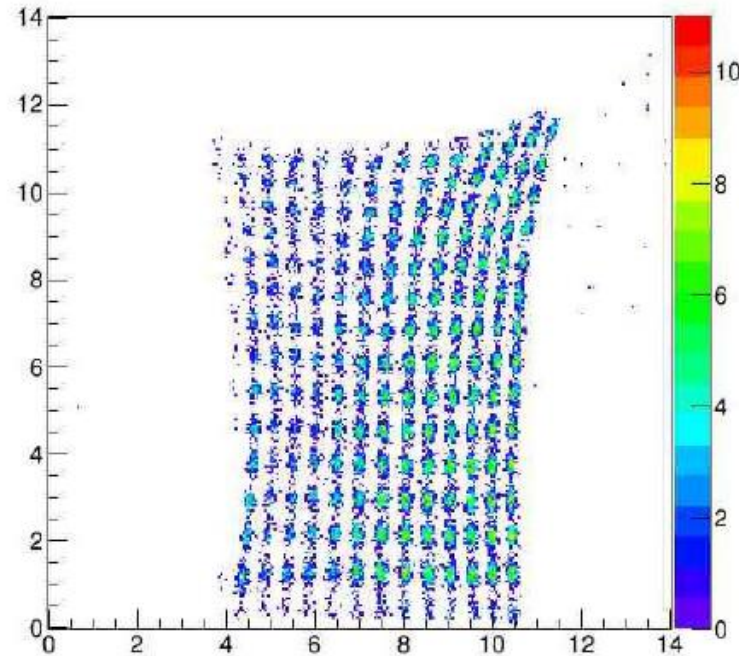
E-field deformations

- Single chip electron depositions in 1[mm] grid
- Height drift due to longer path
- No dead spot between chips

x,y vs time



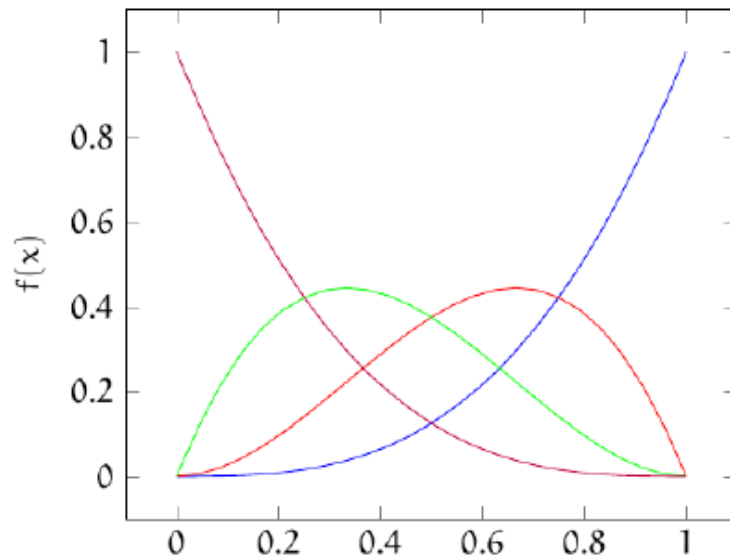
1mm grid scan



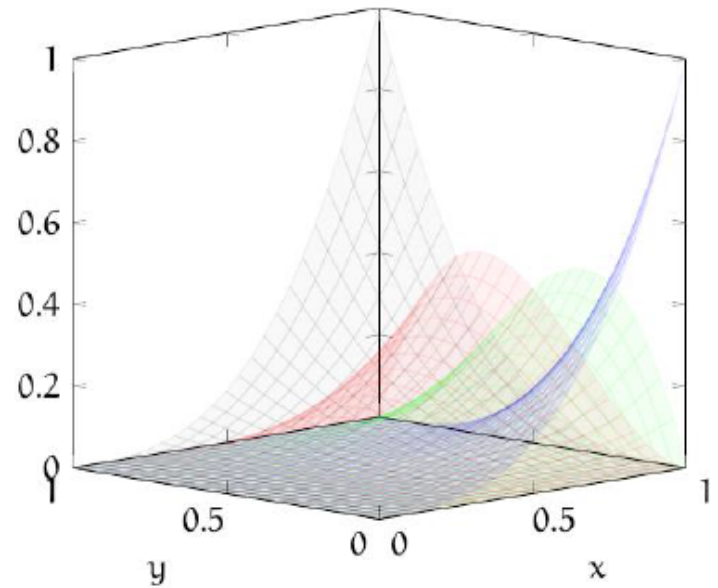
measured with focused UV N_2 laser with 3D adjustable focal point

BiCubic interpolation

- Cubic interpolation in 2 dimensions
- 2 functions: $F(x,y) \rightarrow x'$ and $G(x,y) \rightarrow y'$



4 1D base functions



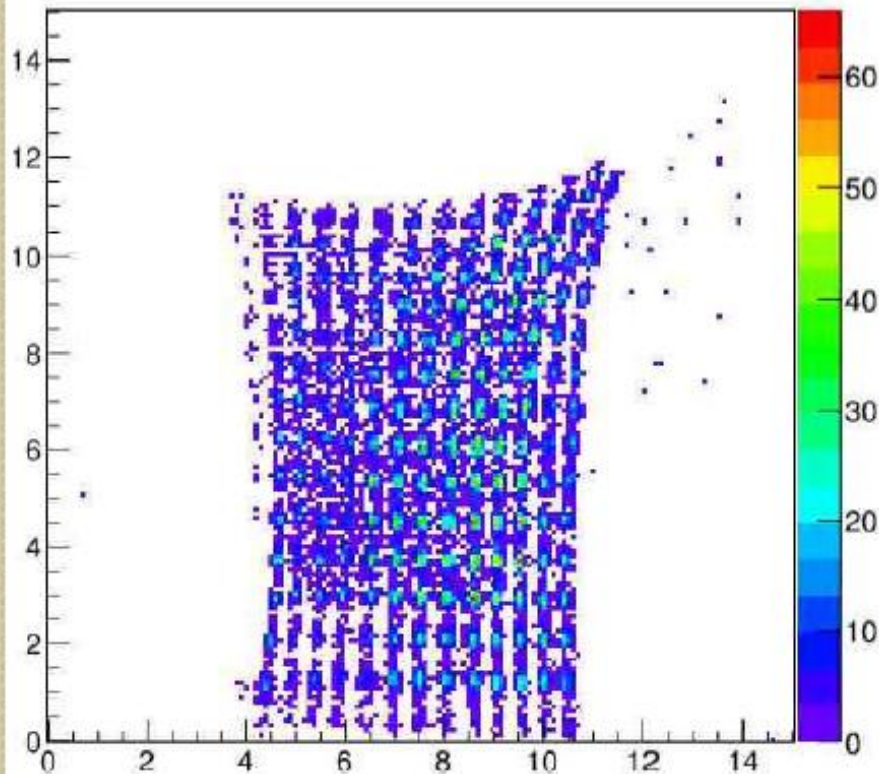
4 of the 16 2D base functions

- Weighted addition of 16 base functions gives smooth surface
- Datapoints and smoothness provide conditions

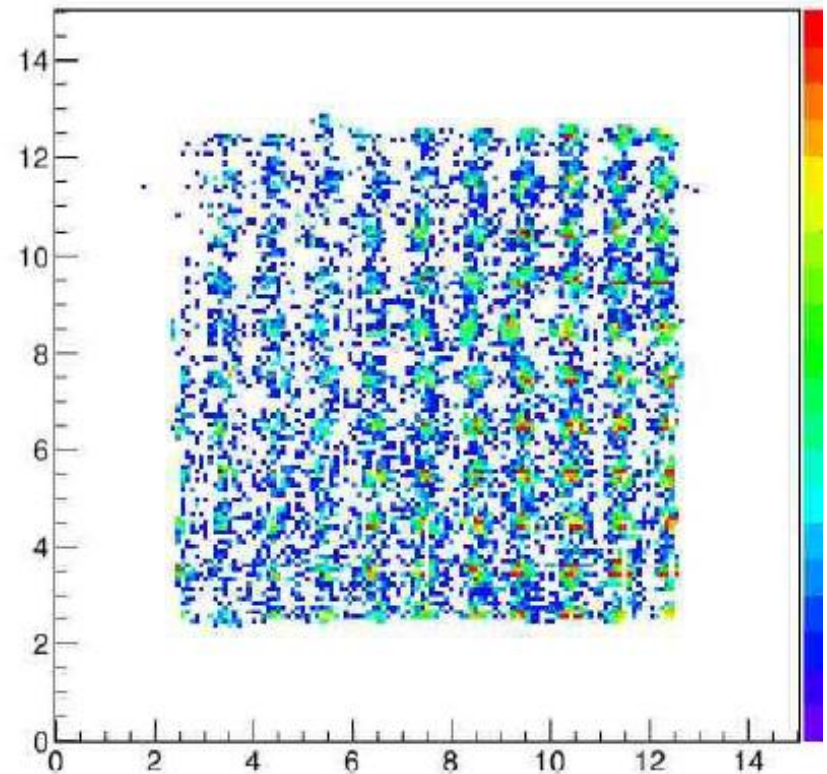
E-field deformations

- 1mm grid scan
- Transforming deformed grid gives uniform grid
- Improvement for spots near the edge

Original Grid



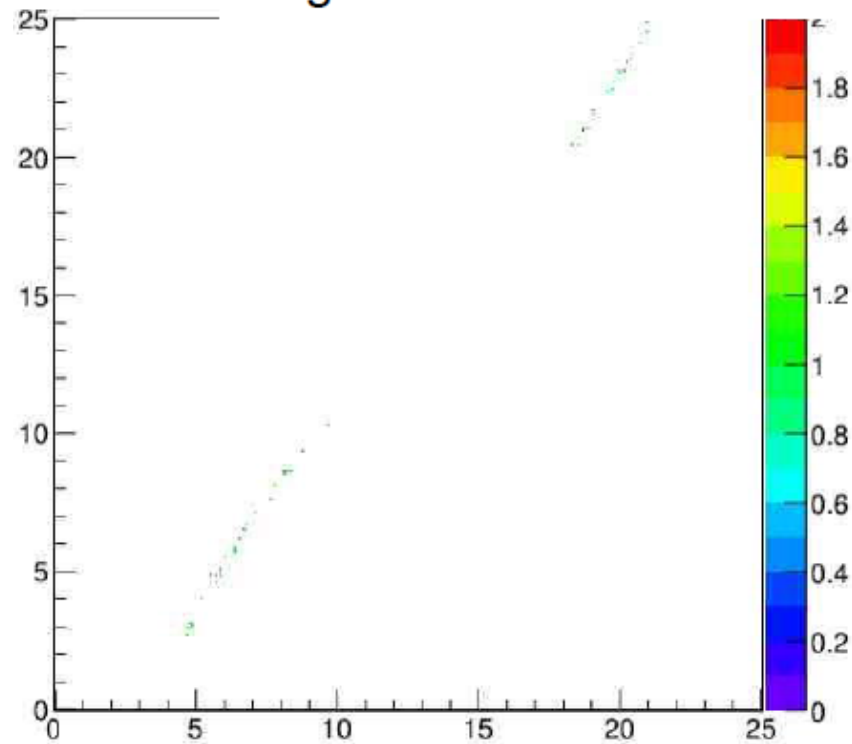
Transformed Grid



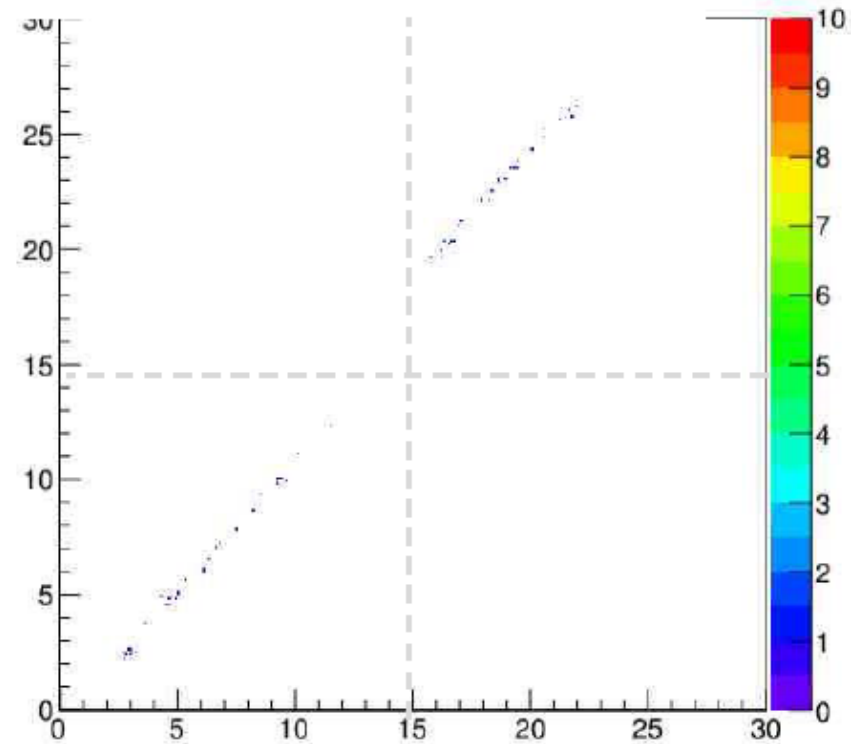
E-field deformations

- Tracks on multiple chips are straightened
- Resulting angle 45 degrees as expected
- Needs distance between chips

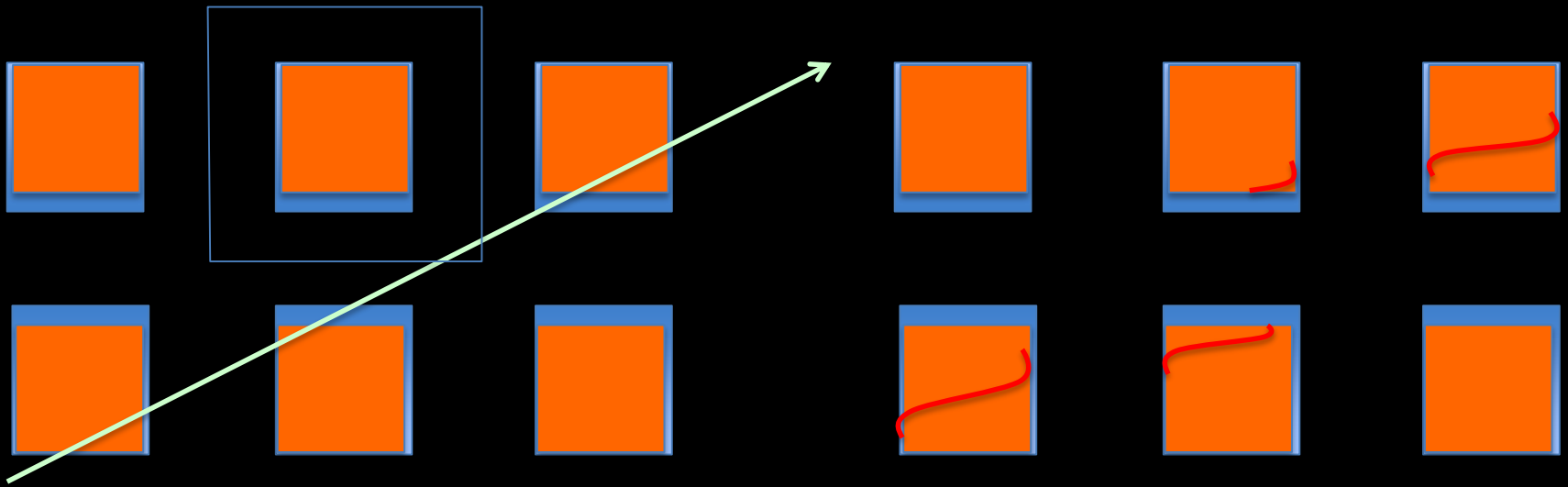
Original Track



Transformed Track



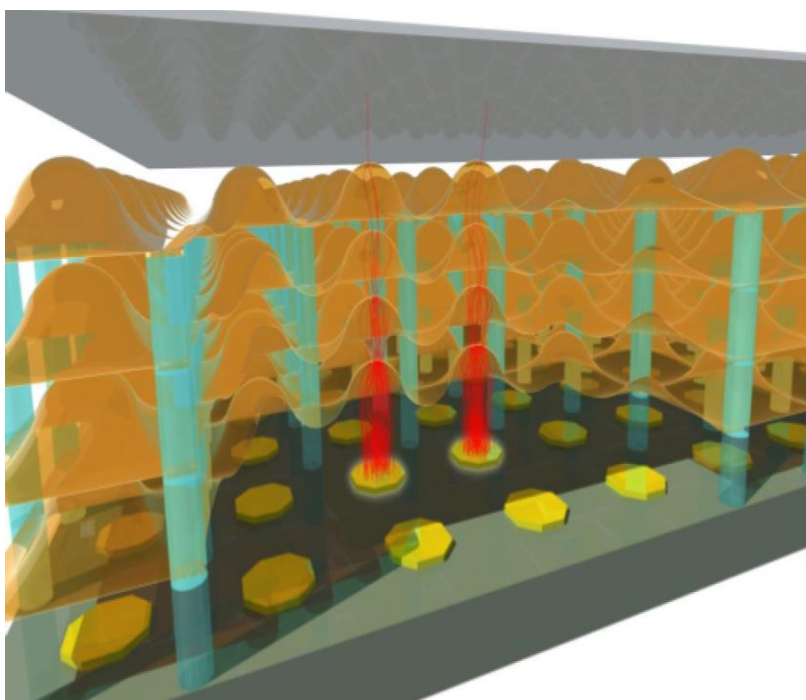
Results from Testbeam T10 (CERN PS), Nov 9 – 12 2016)



Autocalibration

- get initial $f(X,Y) \rightarrow (X',Y')$ from 3D e-field
- make scatter plots of residuals
- modify $f(X,Y)$ until residuals are minimized

Basic correction: $X' = C X, Y' = C Y$
 + $E \times B$ effect



The Tynode: a Transmission Dynode with sufficient yield enabling the construction of Topsy 0.0

On behalf of the Membrane project:

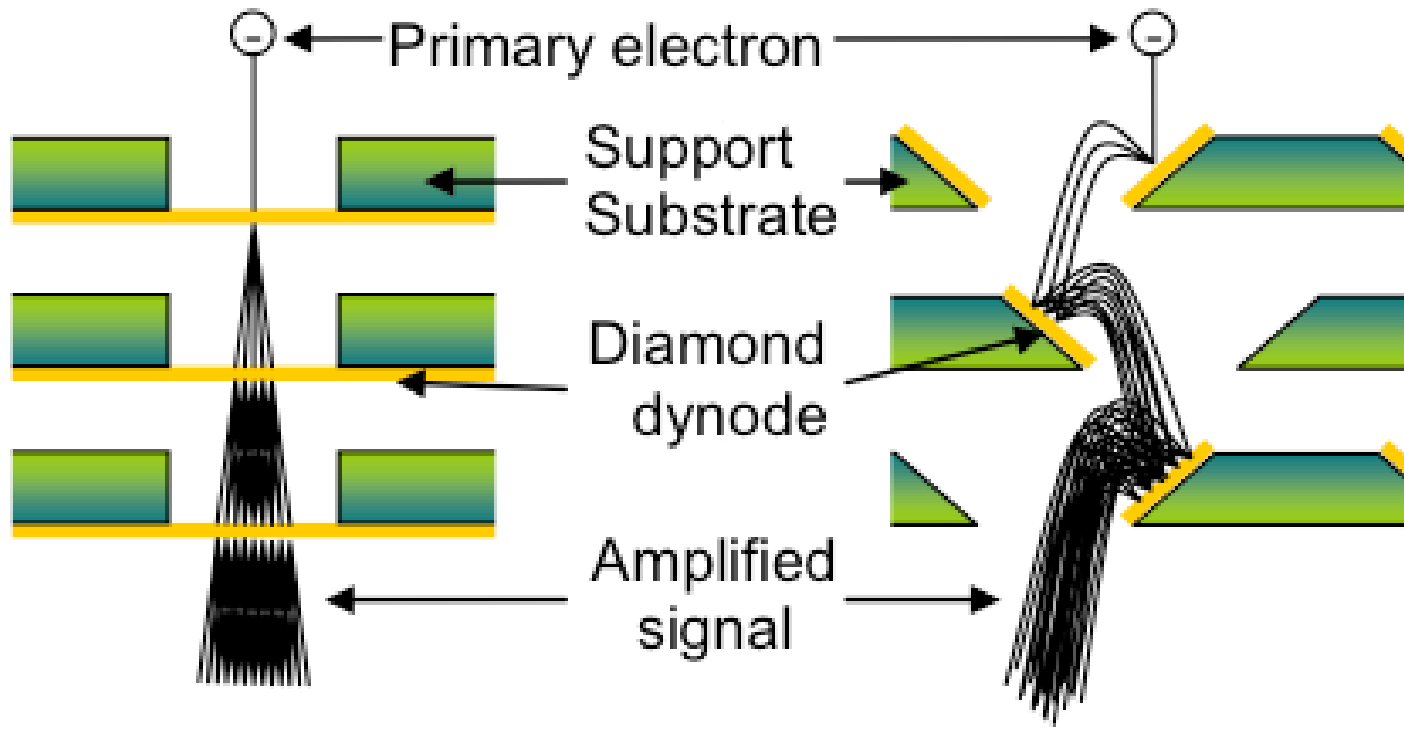
Harry van der Graaf, Conny C.T. Hansson
Hong Wah Chan, Shuxia Tao, Annemarie Theulings, Violeta Prodanović, John Smedley, Kees Hagen, Yevgen Bilevych, Lina Sarro, Gert Nützel, Serge D. Pinto, Neil Budko, Behrouz Raftari

Supported by ERC – Advanced 2012 “MEMBrane” 320764



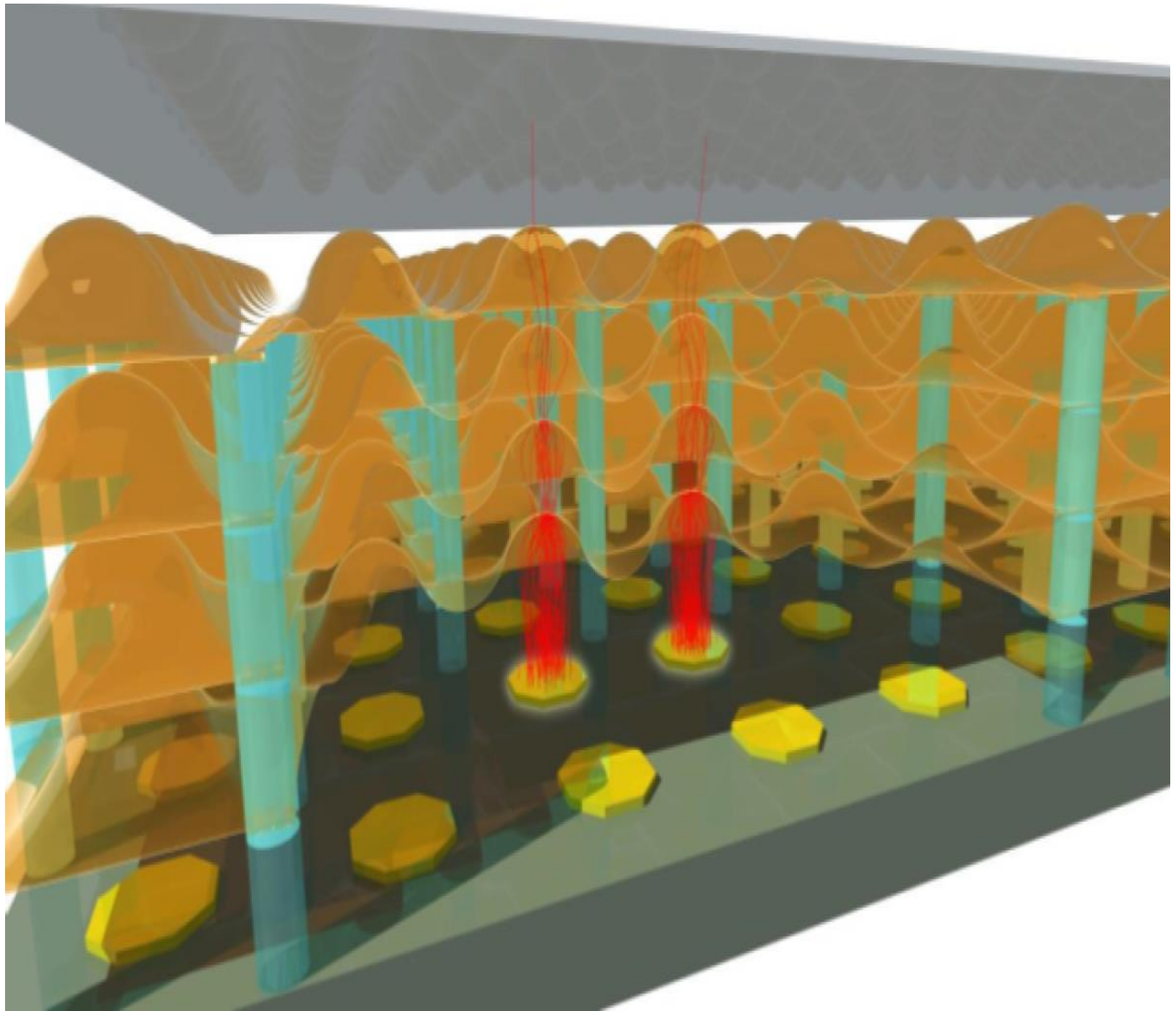
Transmission

Reflection

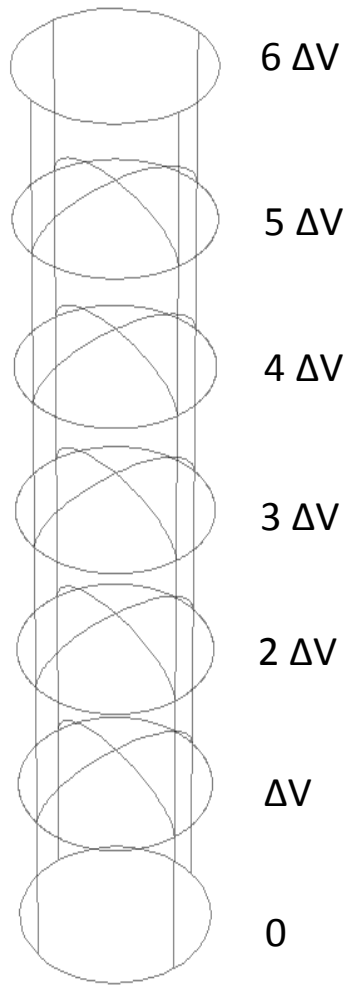


New: the Transmission Dynode

Tynode[®]
Trynode[®]



The **T**ransmission **Dynode** → Tynode

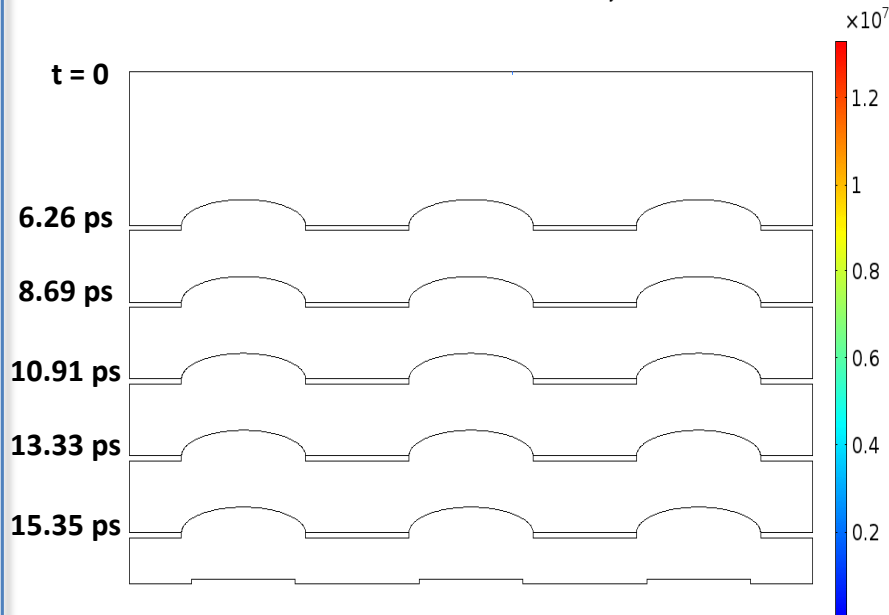


- Similar to PMT dynodes, but with amplification through transmitted secondary electrons through nanoscale thickness membranes (**Tynodes**)
- The Tynodes offer effectively **dark noise free** electron multiplication
- A **compact device** (see top right) can be fabricated with a photocathode on top stacked tynodes and collector readouts on the bottom.
- The pixelated detector allows for **spatial resolution** (imaging)
- The high bias field between the membranes, and the tailored dome shape of the membranes allow for **operation in high B-field**.

Stacked Tynodes Simulations

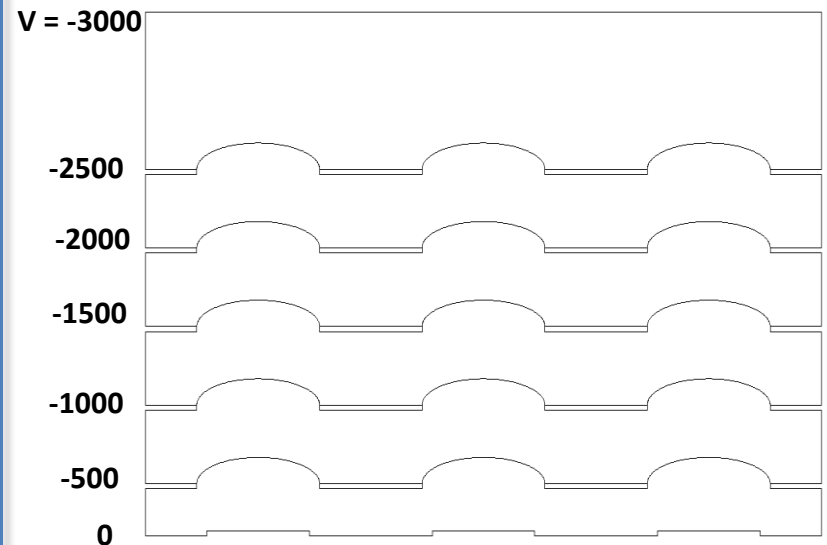
More compact → faster detector

Time=4.0404E-13 s Particle trajectories



- Simulated device thickness ≈ 100 microns
- Time between tynodes ≈ 5 ps
- Time spread of generated electron cloud below ps timeframe (path uniformity)

Performance in magnetic fields



- Operational in 1 T magnetic fields

The Timed Photon Counter – TiPC – “Tipsy”

Photocathode → Tynodes → TimePix chip

TimePix chip:

- 256 by 256 pixels with 55 μm pitch
- Surface = 1.4 cm by 1.4 cm

Matching Tynodes (Transmission Dynodes):

- Diameter = 30 μm
- Pitch = 55 μm
- Separation = 25 μm

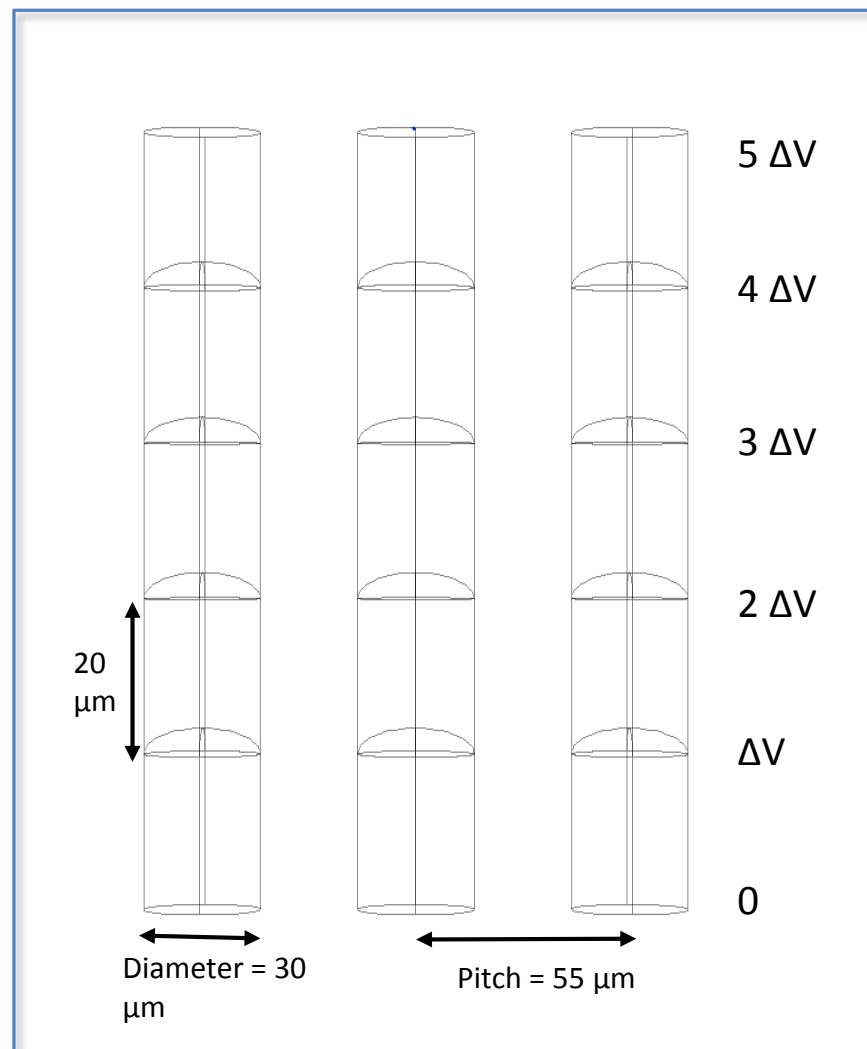
Sensor Charge Requirements:

	Timepix 1 (2006)	Timepix 3 (2013)	Timepix FG
Min. detectable charge	>750 e-	>500 e-	>60 ke-

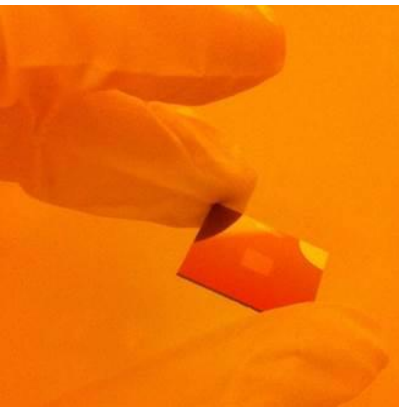
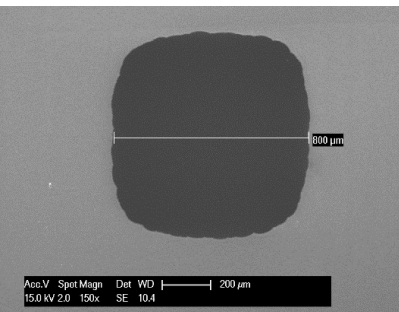
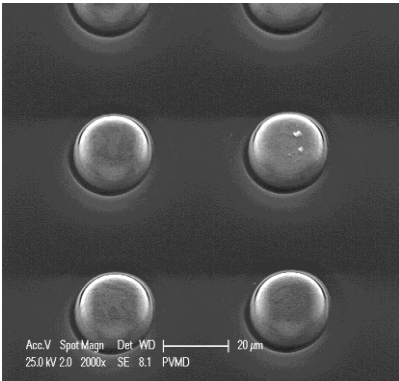
Tynode gains:

Gain = $\delta^N = 4^5 = 1\text{k} \rightarrow$ threshold

Gain = $\delta^N = 4^8 = 60\text{k} \rightarrow$ 1 Volt digital



Membrane Fabrication



Fabrication through combinations of lithography, etching, and atomic layer deposition

Materials considered: Si_3N_4 , Si-rich Si_3N_4 , Al_2O_3 , SiC, MgO

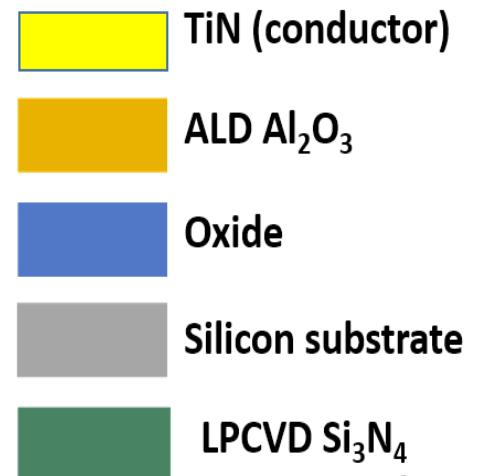
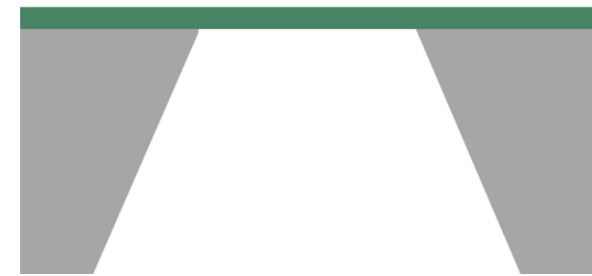
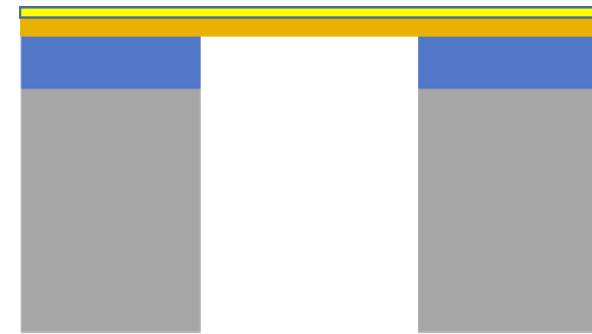
TiN used as conductive layer to reduce charging effects with minimal effect on secondary electron yields.

Array of tynodes

- Thickness: 5-40 nm
- Diameters: 10, 20, 30 μm
- Array size: 256 by 256

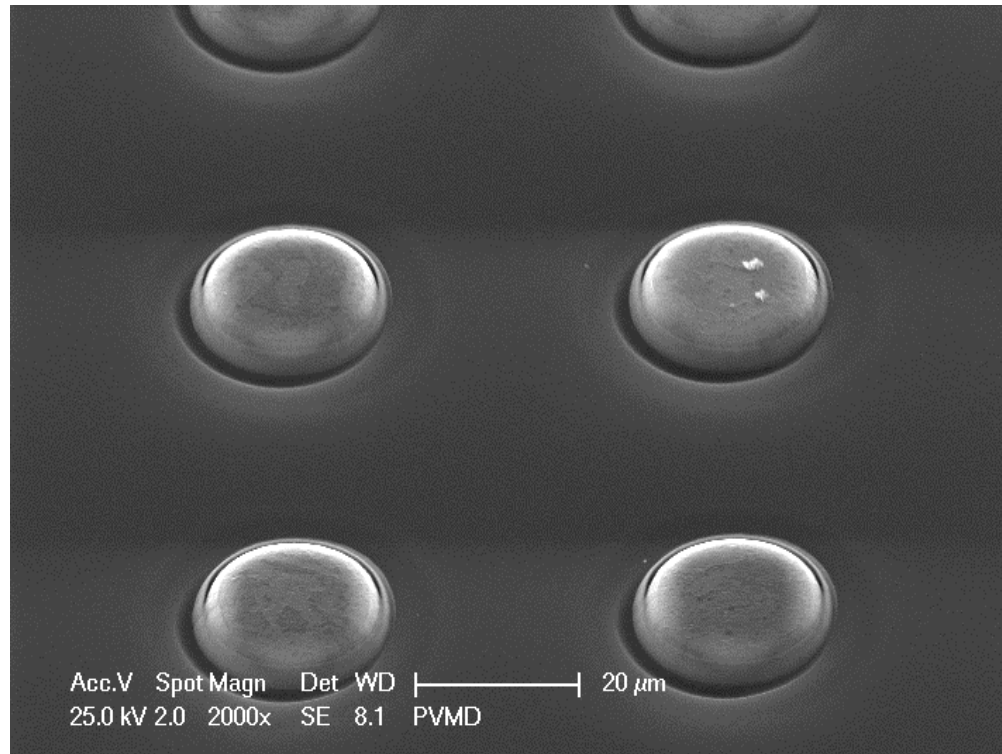
Large area tynodes for testing purposes

- Thicknesses: 40-200 nm
- Diameters: 50, 100, 300, 1000 μm

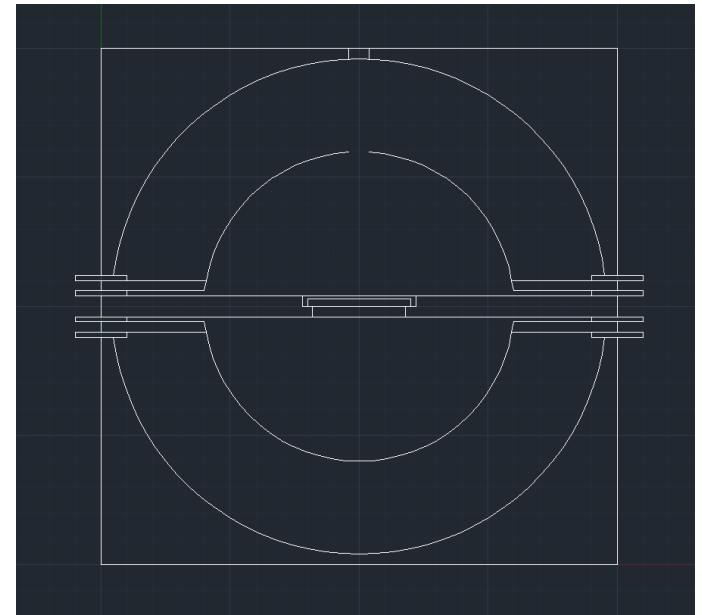
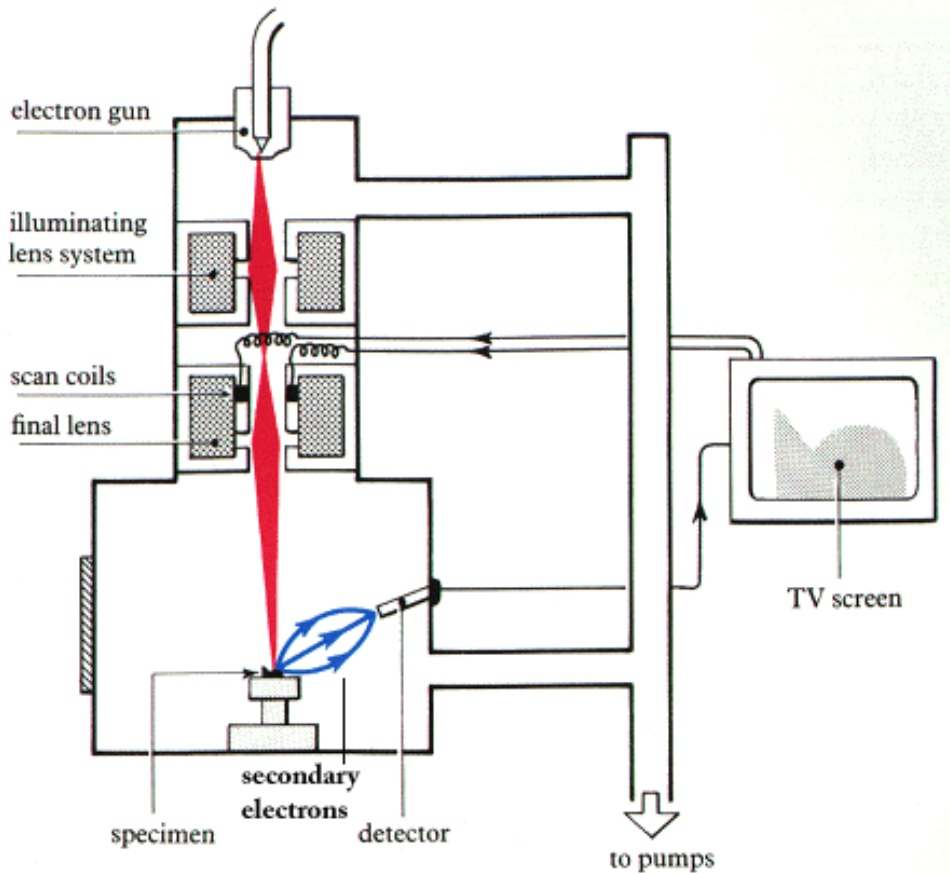


Path towards first prototype

- We have created many tynodes of various sizes and materials
- Most recently, we have achieved transmission yields of >3 with 5 nm MgO membranes, coated with 2.5 nm TiN, without other special surface treatments
- Now working towards building a first prototype device



SEY Measurement 1 in SEM



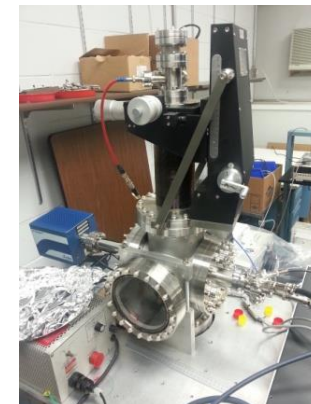
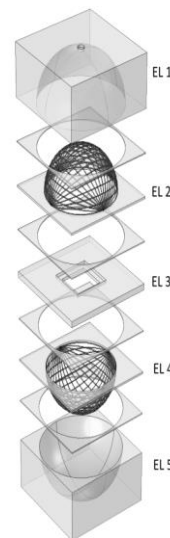
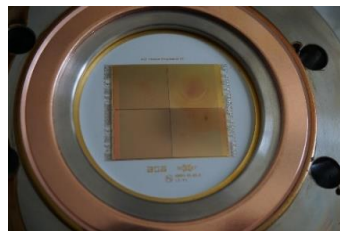
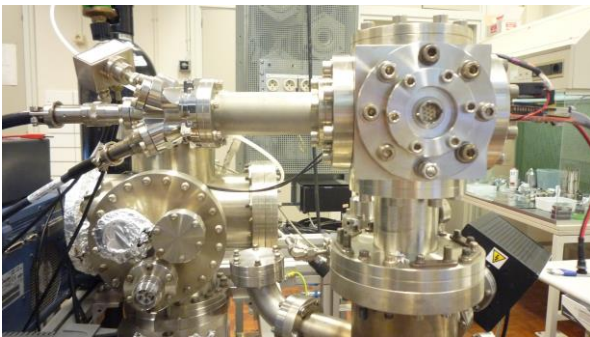
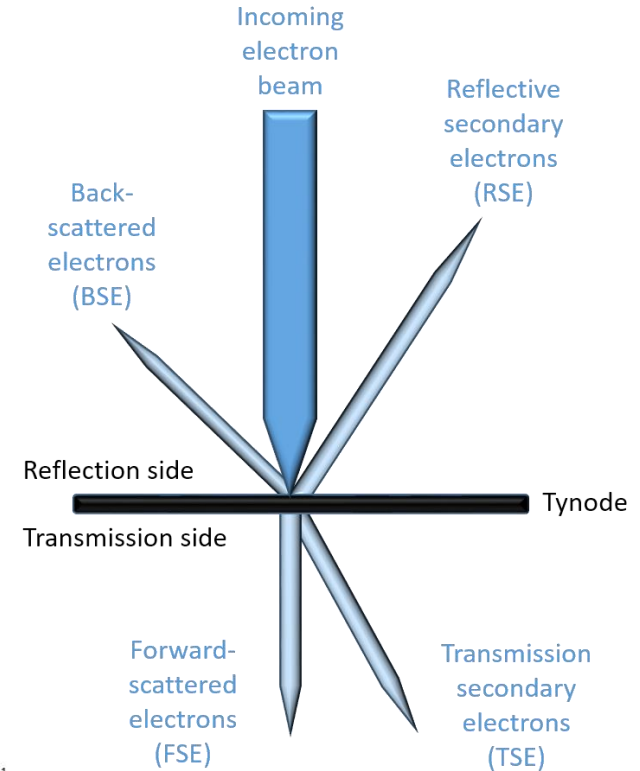
Dual Faraday Cup in SEM
made at Nikhef

SEM/TEM to measure reflection/transmission SEY@
Particle Optics Group TU Delft by **Alexander and Kees**

Measurement Techniques

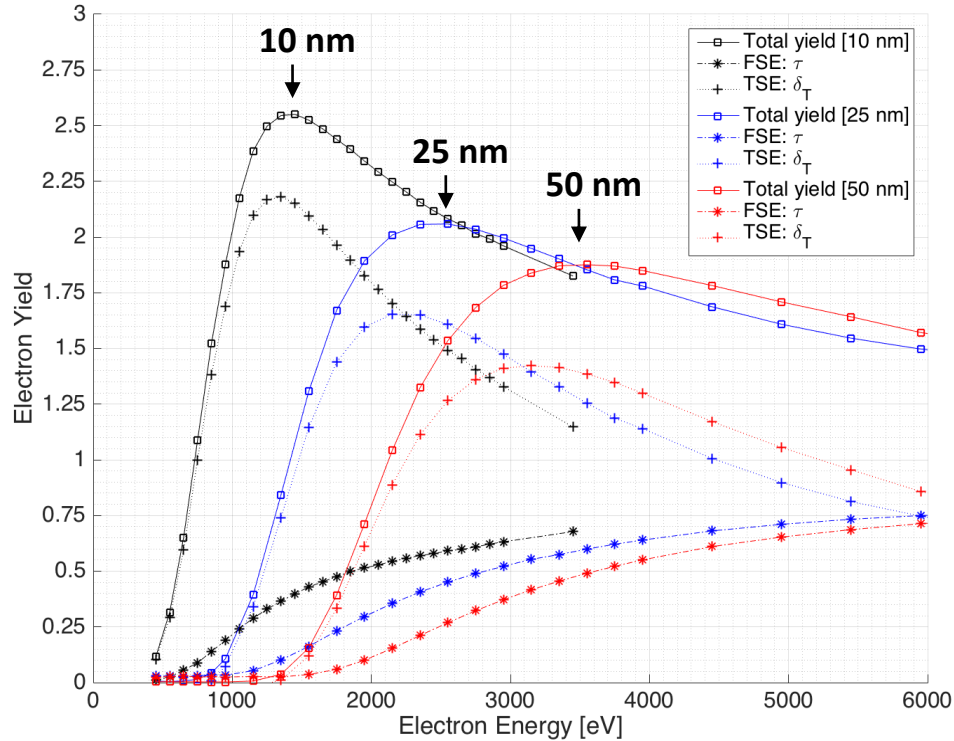
Search for material and/or surface treatment for transmission yield goal of 4.

- Collaboration using four unique vacuum systems optimized for different aspects of dynode/tynode measurement
- Reflected and transmitted secondary electron yields for different membranes or thin films
- Measure under different electron beam fluxes or pulsing schemes
- Consider different surface terminations for improving electron yields



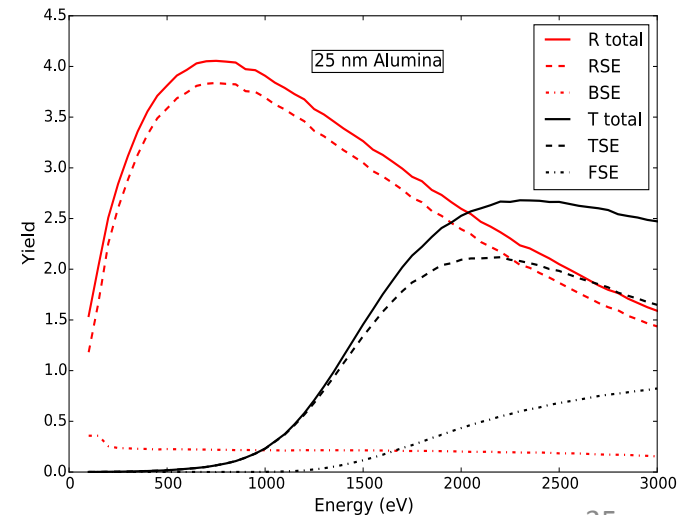
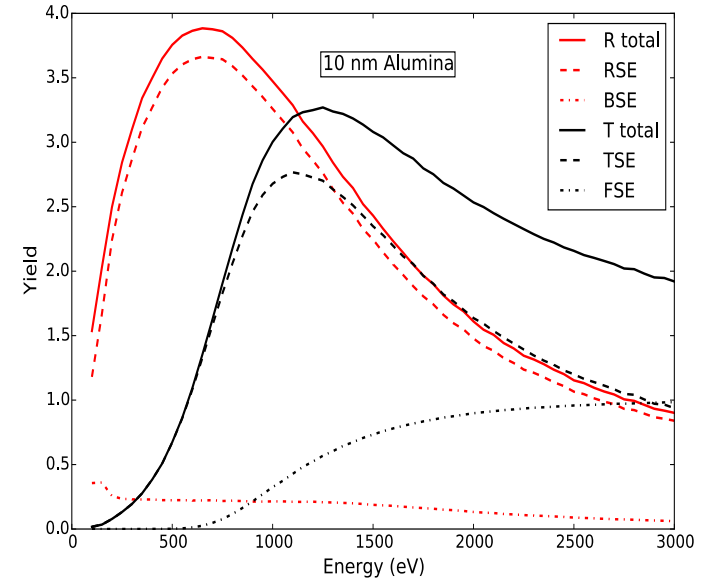
Al₂O₃ Measurements and Simulation

Measurement



- A decrease in yield, combined with increase in optimum primary electron energy is observed as a function of sample thickness
- Good correlation to measurements seen for the simulations.

Simulations



SEM measurement setup: E-field setup

Sample: MgO [5nm] + TiN [2.5 nm]. 64x64 array with 30 μm diameter. (Same sample when we obtained ~ 3.2)

Electron beam energy: 1500 eV

Electron beam current: 0.12025 nA

HFW: 12.8 μm

Magnification: 10000x

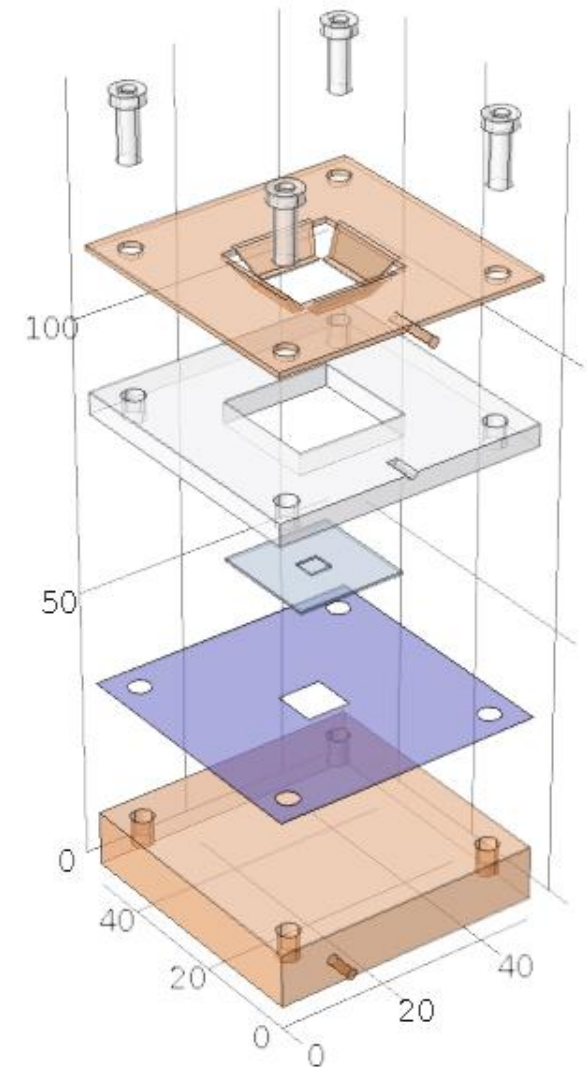
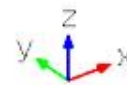
Distance between Tynode and collector: 30 μm

- 100 μm (?)

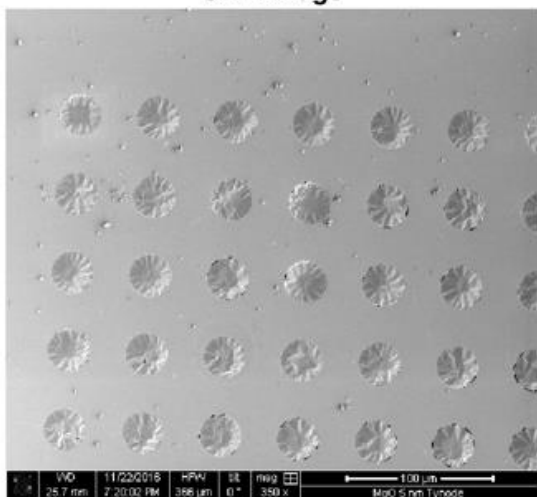
Method:

- Apply bias
- measure background
- Irradiate a Tynode for 20 sec.
- Locate next Dynode
- repeat 5 times

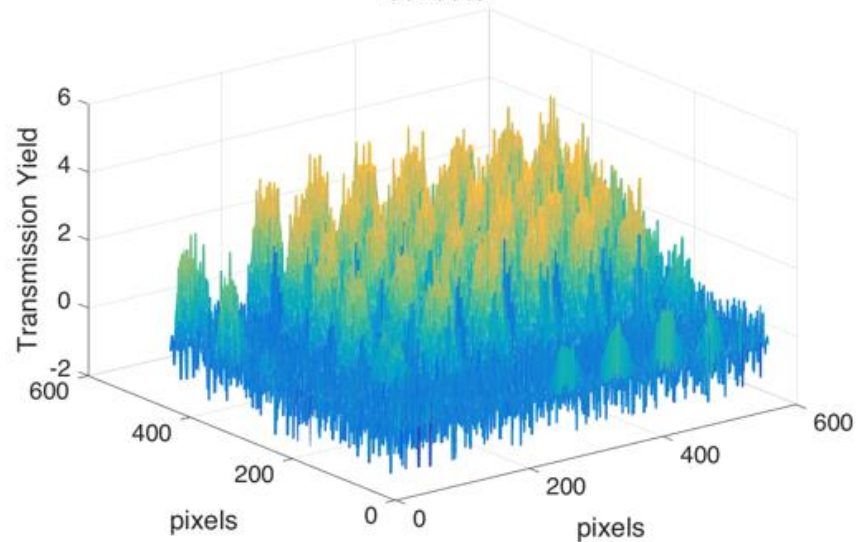
Calculation: $\text{TEY} = I_{\text{collector}} / I_{\text{beam}}$



SEM image

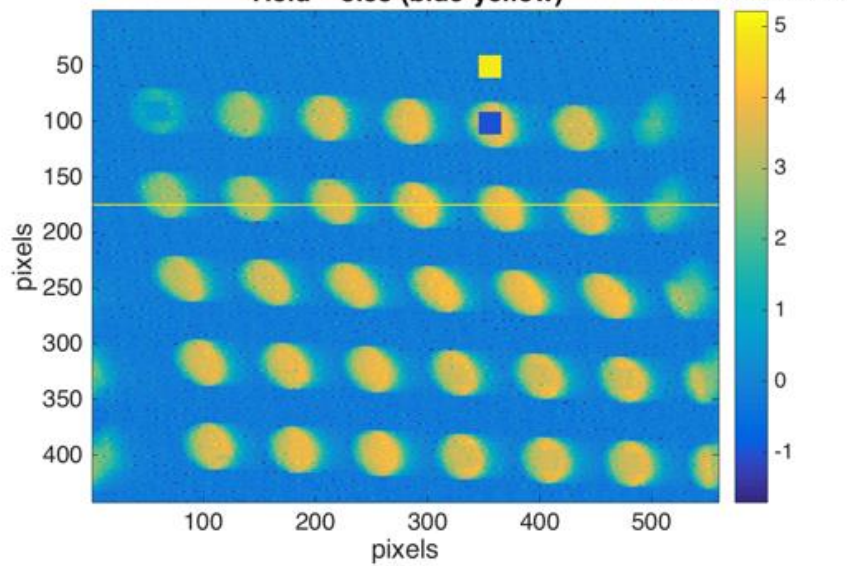


collector

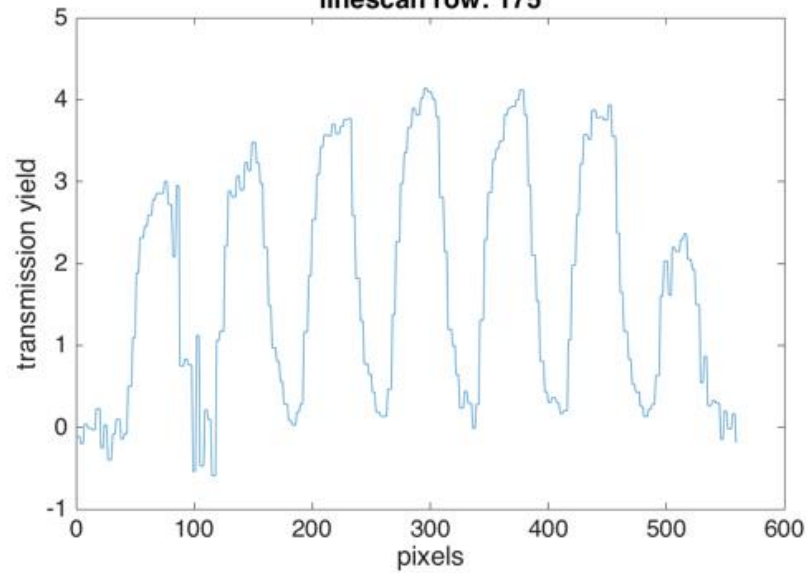


Yield = 3.58 (blue-yellow)

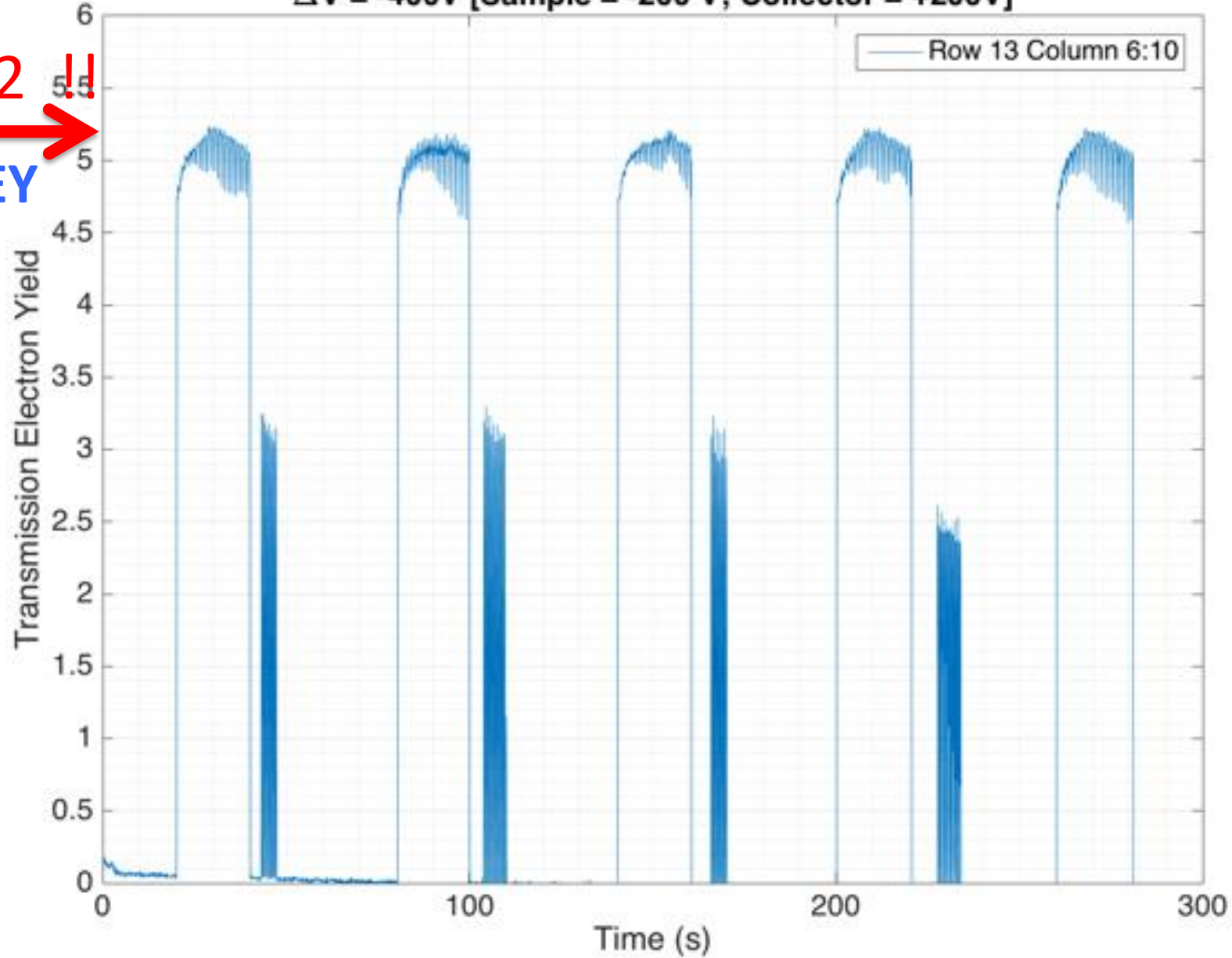
Transmission Yield



linescan row: 175



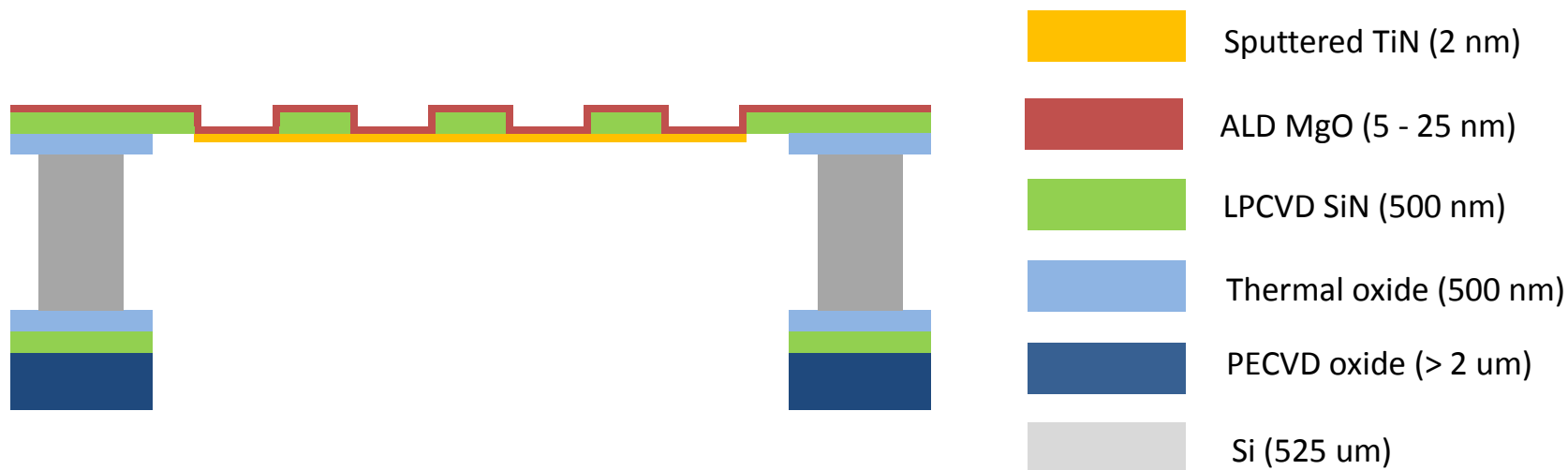
$\Delta V = -400V$ [Sample = -200 V; Collector = +200V]



!! 5.2 !!
TSEY

Timed Photon Counter – Tipsy 0.0 – Fabrication of First Prototype

Finalized layout of MgO domes



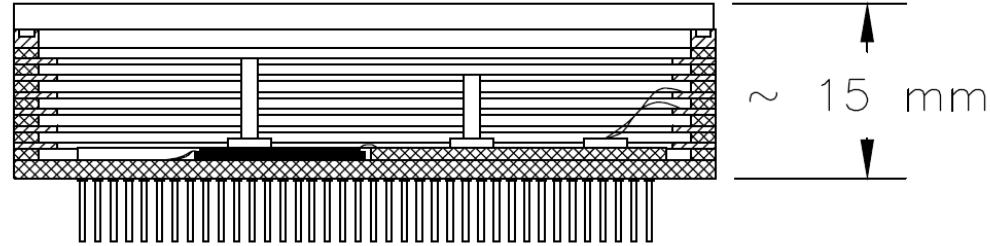
- We intend to manually stack 5 of these tynodes and place the stack above a TimePix-1 chip
- When in a close stack, we may achieve higher yields from close, extracting fields: There is a report¹ that, with a single Si membrane, yields of 200 has been reached due to a strong extracting field. We may have an even much higher extracting field!

1) Qin, Kim, Blick. APL **91**, 183506 (2007).

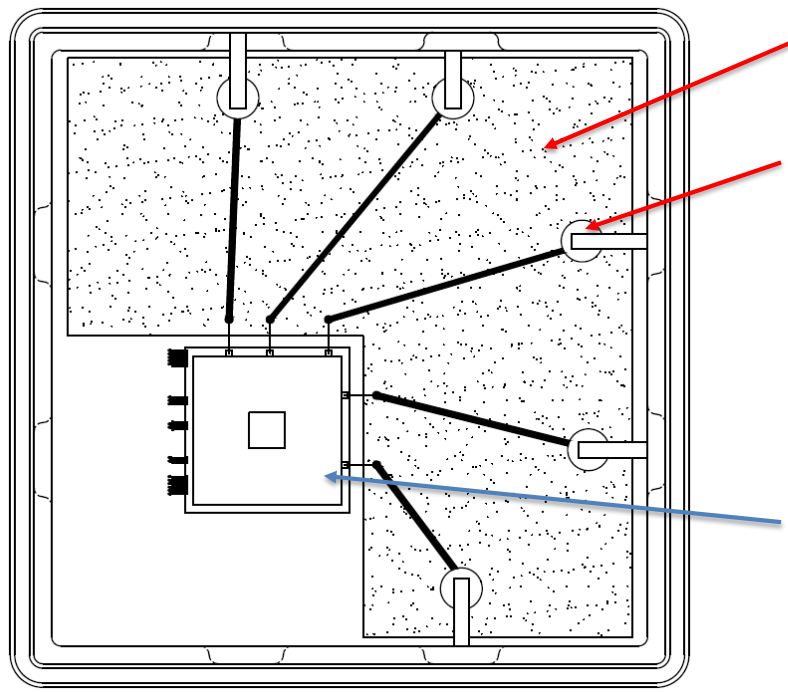
Concept - Fabrication **Tipsy 0.0** into a **Photonis PLANACON™** Style Device

TimePix-1 pixel chip on Kyocera carrier board

- Ultra high vacuum compatible, sealing with Planacon window, photocathode compatible



Tipsy 0.0 will be limited to the 10 ns bin size of TPX-1 or 1 ns bin size of TPX-3
a new TimePix NN with 10 ps time resolution



Fan-out ceramic with metalized top-traces for HV distribution

Metal studs and weld ribbons to electrode rings

Backside metalized ASIC (TIMEPIX) with tynodes eutectic bonded into envelope + wirebonds



classical
gaseous

The Quad: a general purpose modular readout system for TPCs

+ reaching transmission secondary electron yield TSEY = 5.2

Harry van der Graaf
Nikhef & TU Delft

8th Symposium on Large TPCs
Diderot University
Paris, France, Dec 6 2016